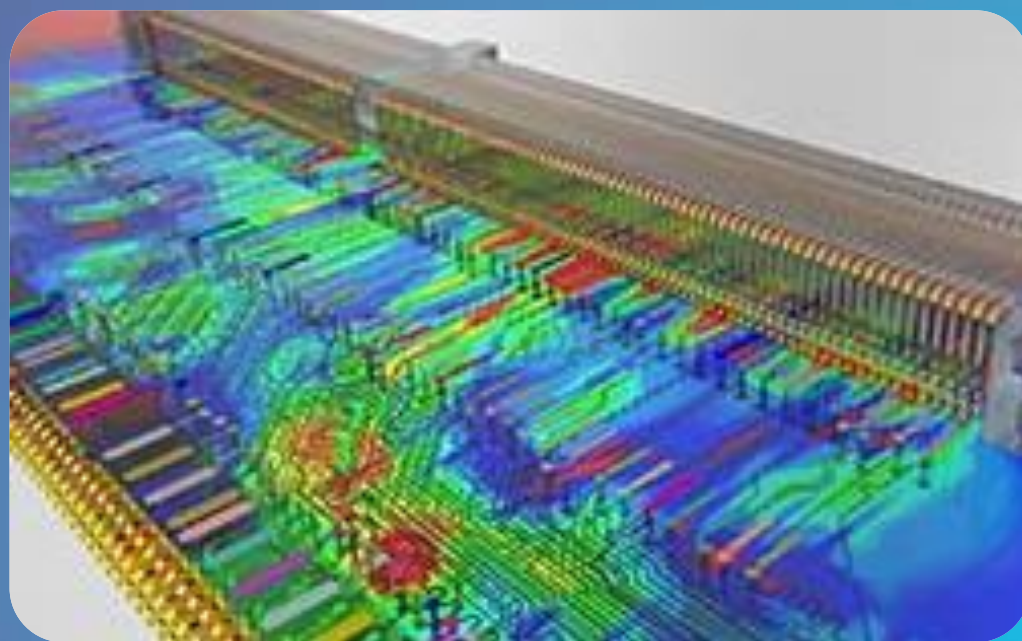




ANSYS SIwave信号完整性仿真 基础及新功能介绍

艾迪捷信息科技有限公司（上海）有限公司

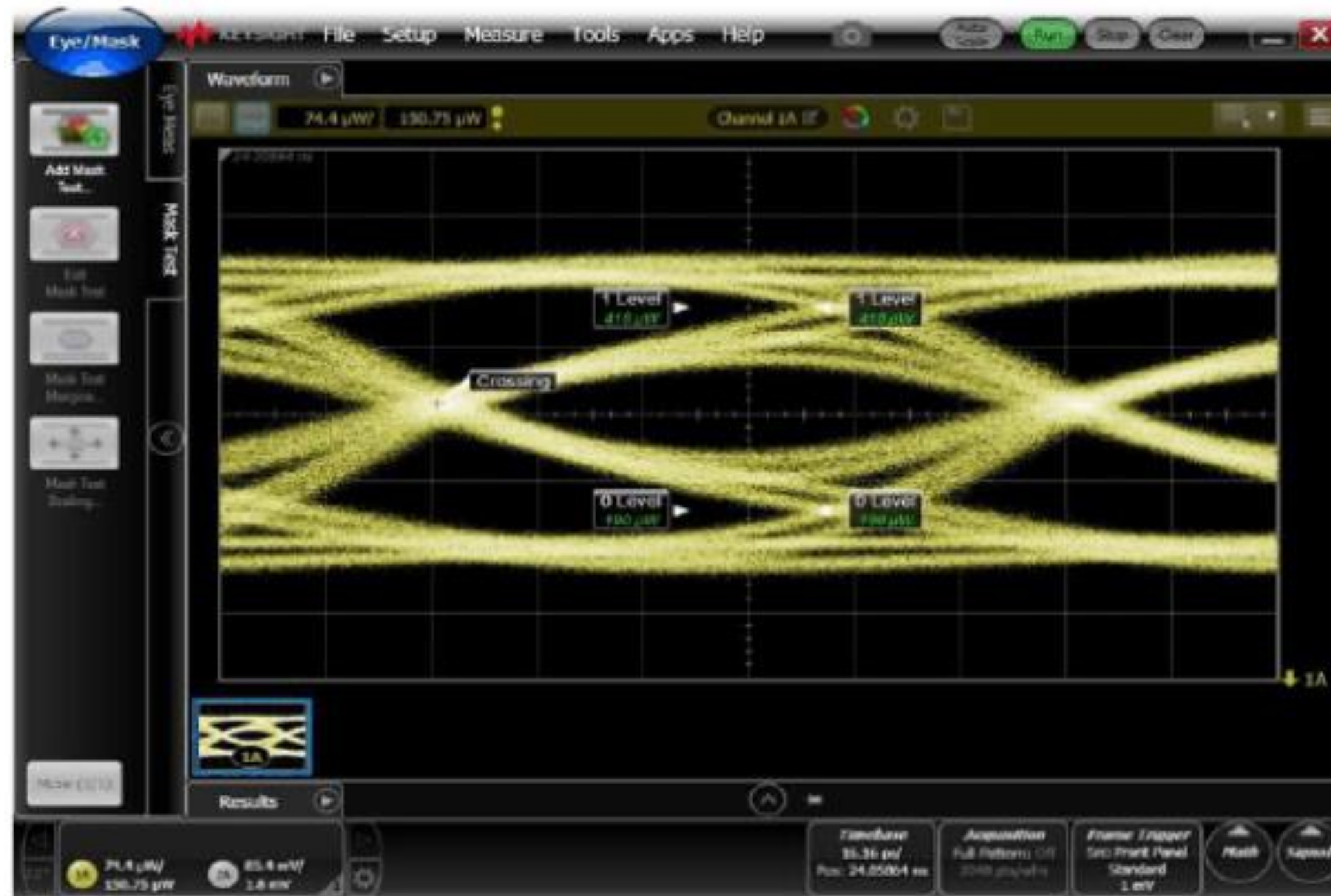
IDAJ-CHINA

高频电磁场技术经理 资深高频技术工程师 刘捷

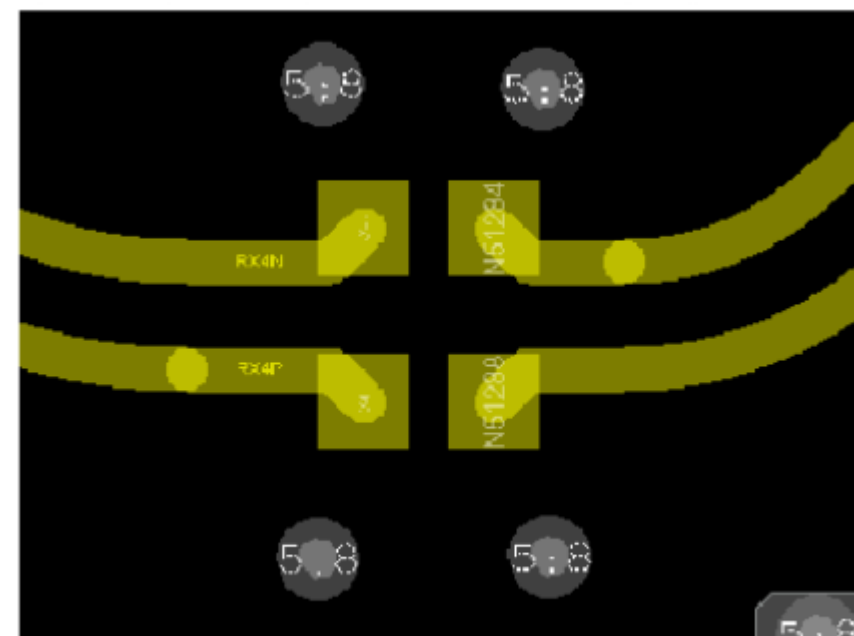
目录

1. SIPI仿真必要性
2. SIwave功能介绍
3. 新版本新功能

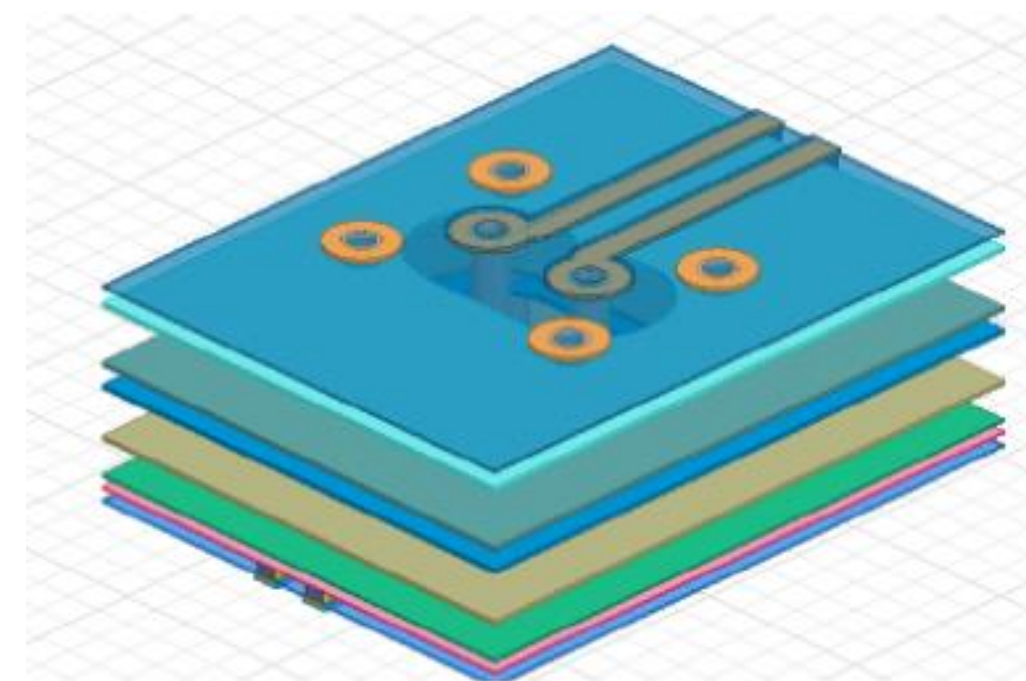
信号完整性设计案例



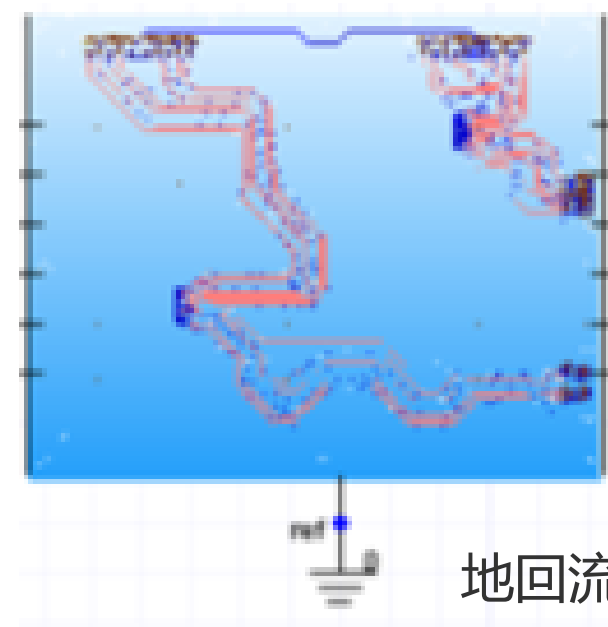
信号完整性设计案例



器件焊盘走线阻抗不连续



信号过孔阻抗不连续



地回流问题

信号完整性设计案例

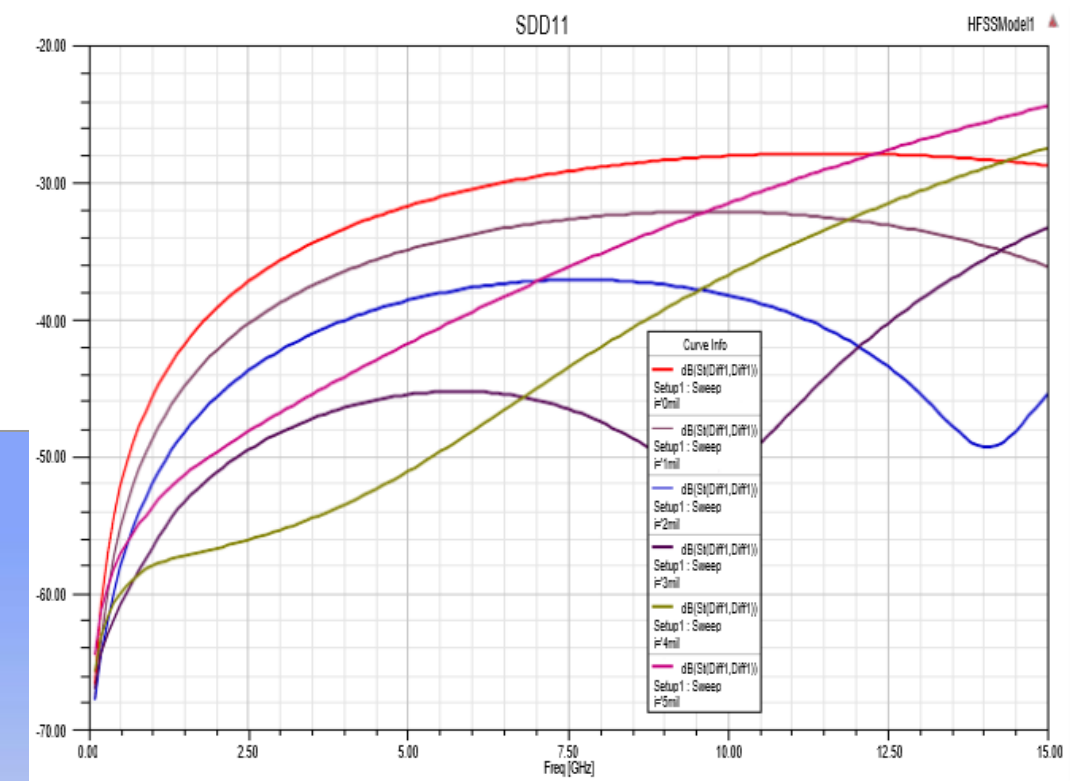
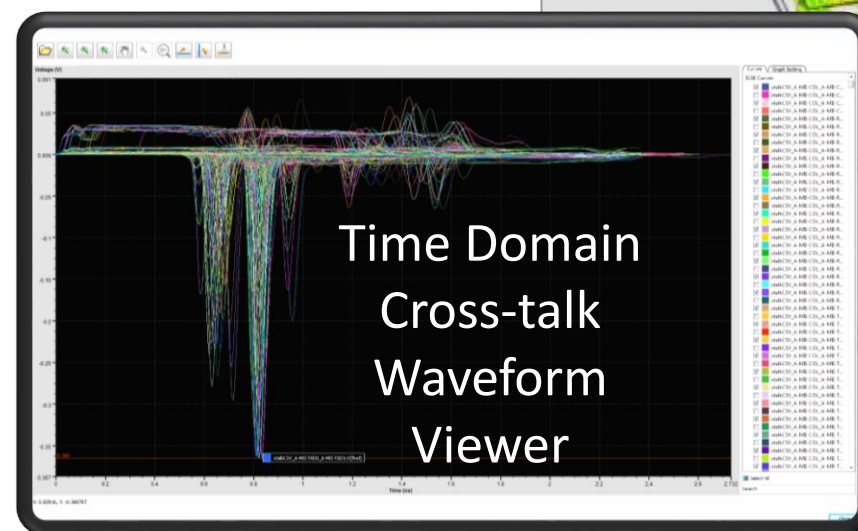
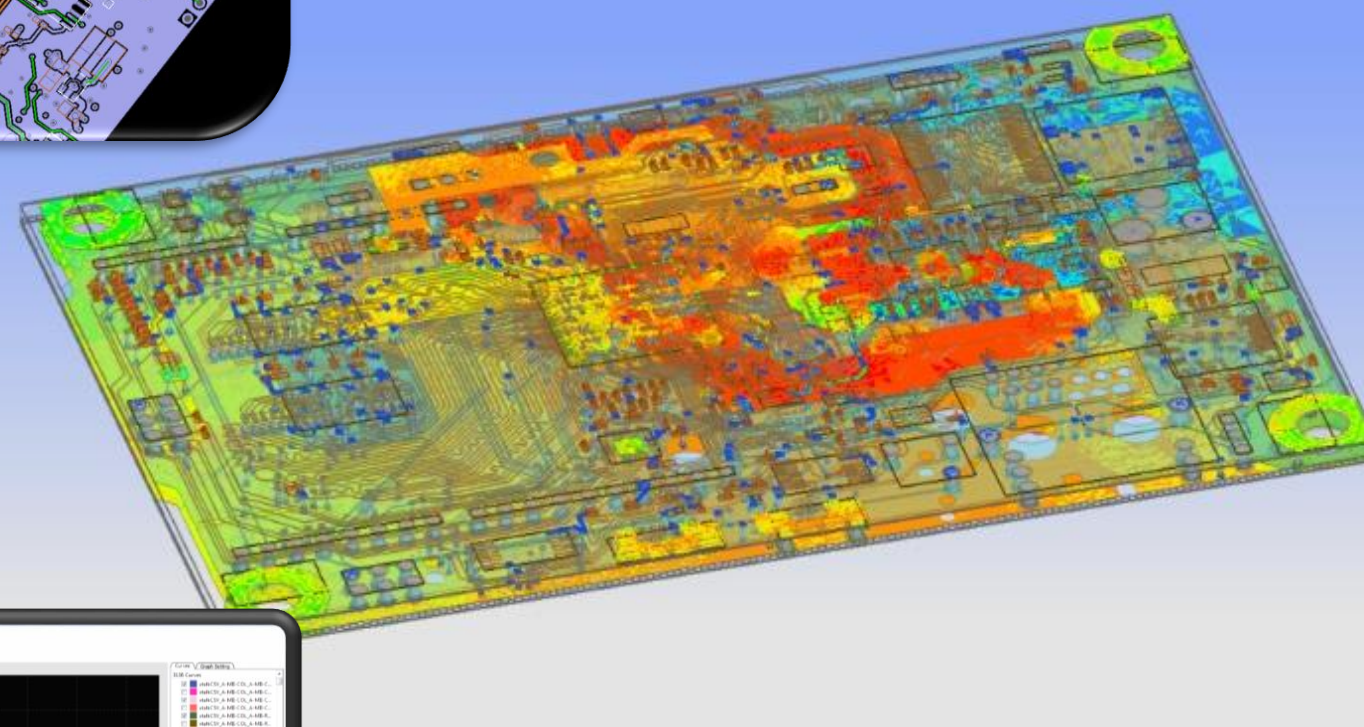
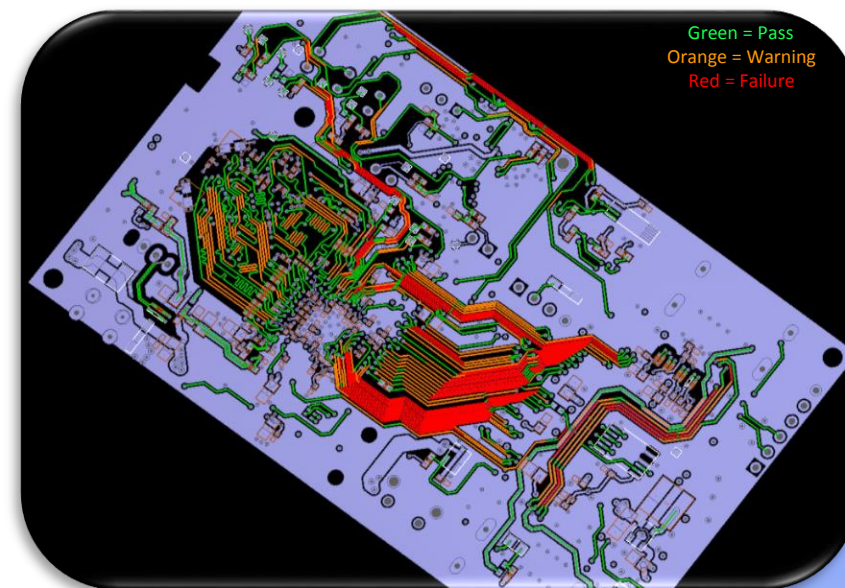


图 6 (回波损耗)

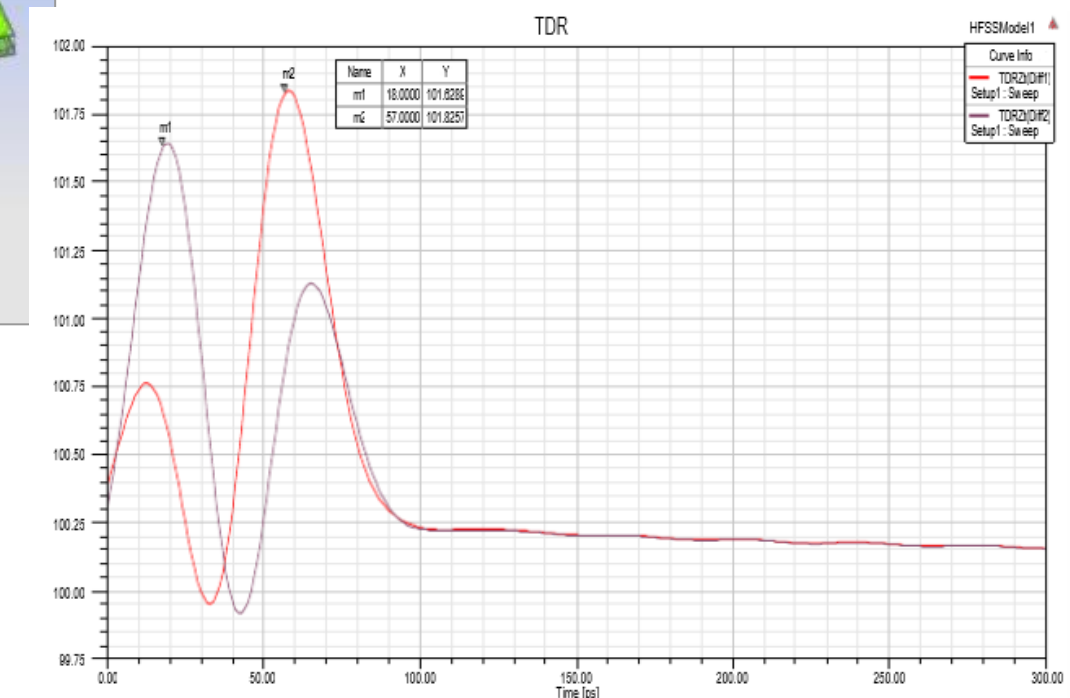
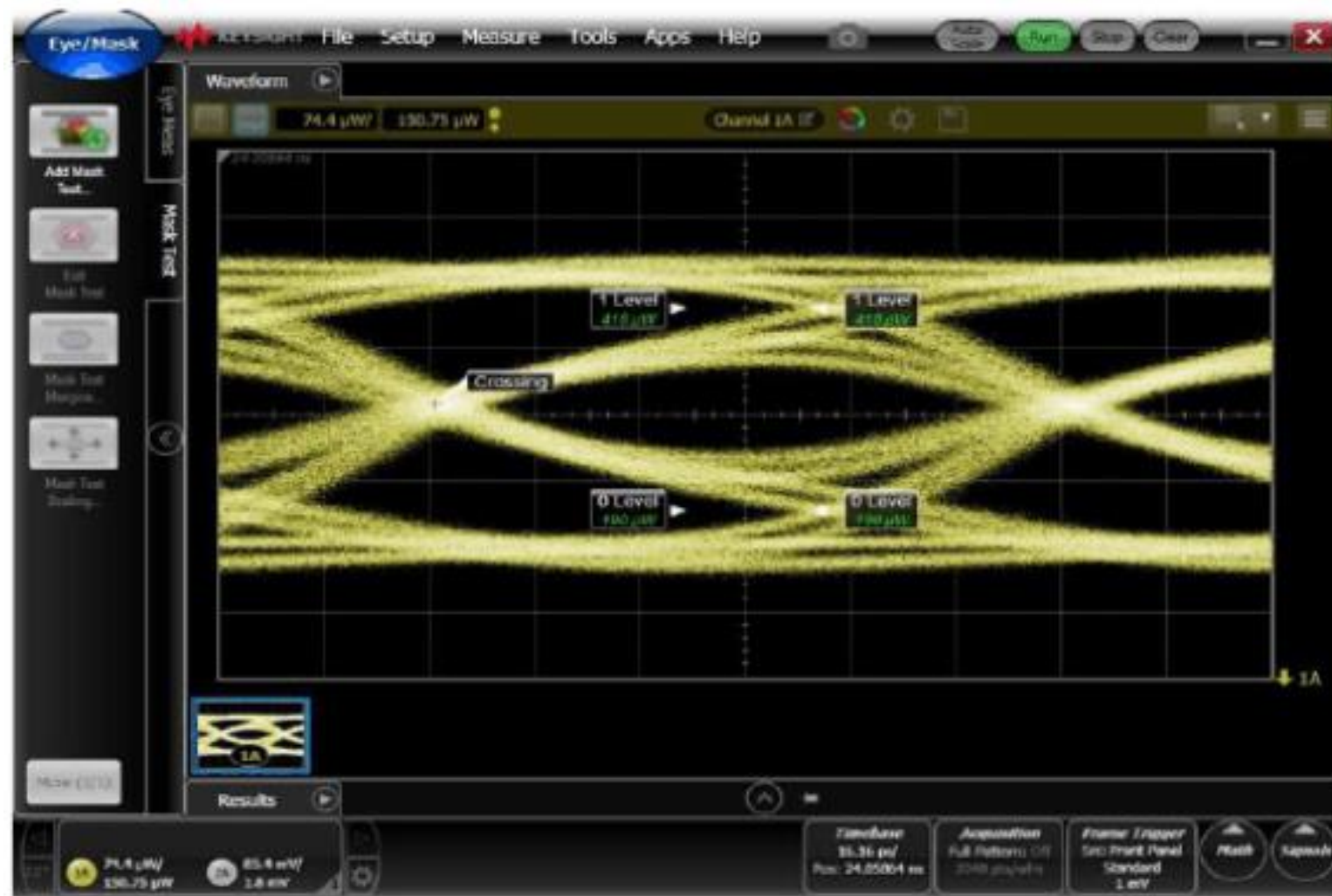
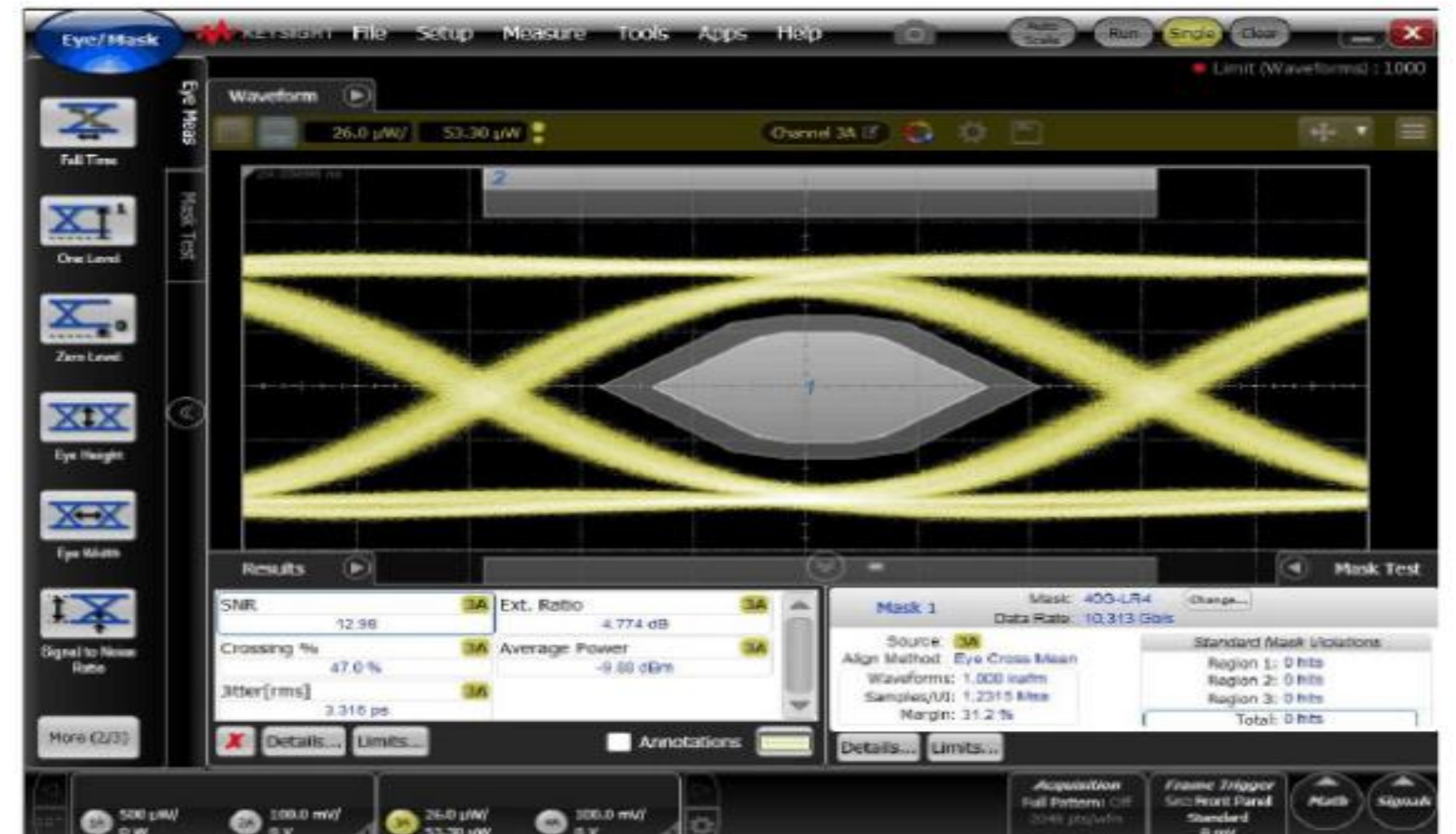


图 10 (TDR, 99-102Ω 之间)

信号完整性设计案例

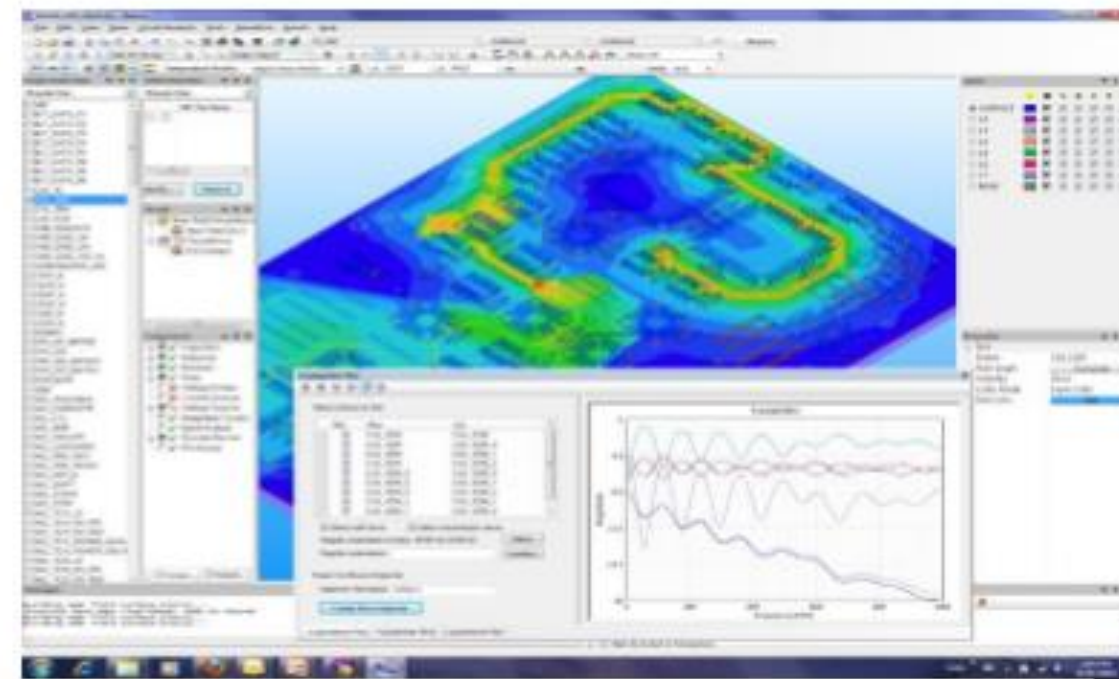
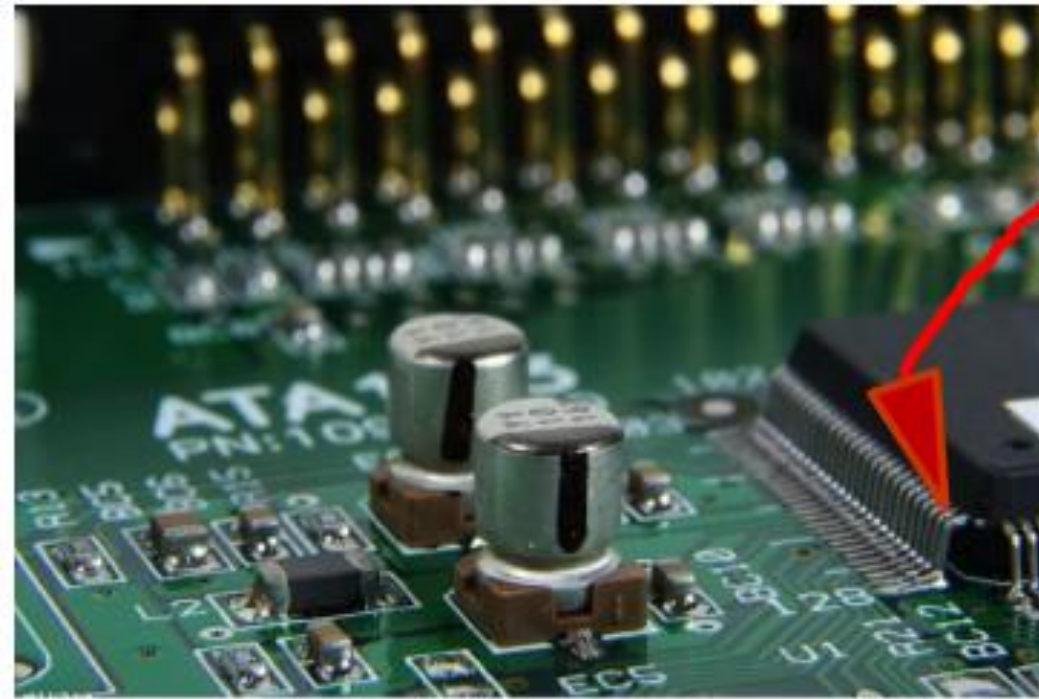


优化前眼图



优化后眼图

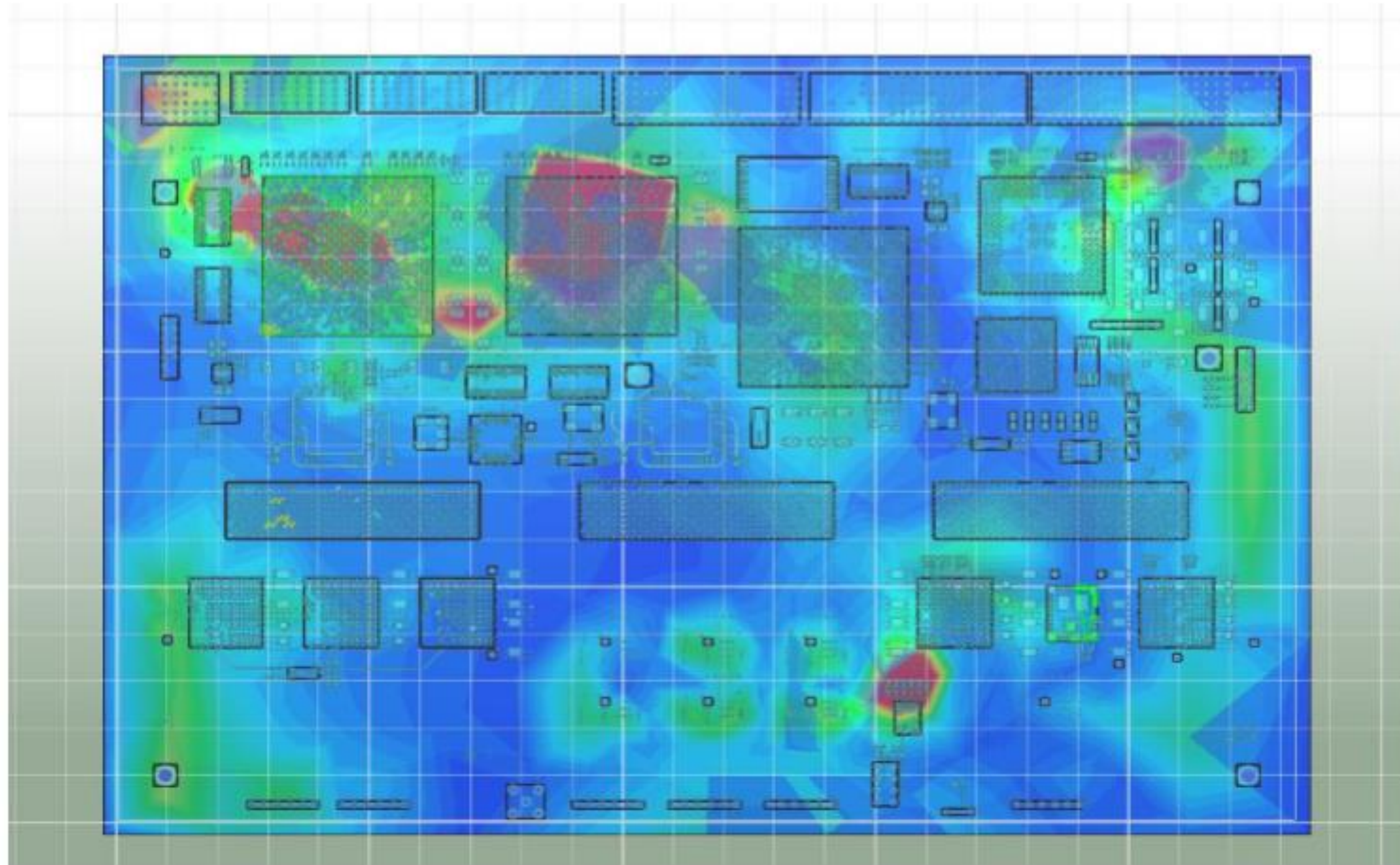
PCB电源噪声干扰案例



测试发现芯片电源电路附近存在较大噪声

原始PCB布线导入SIwave

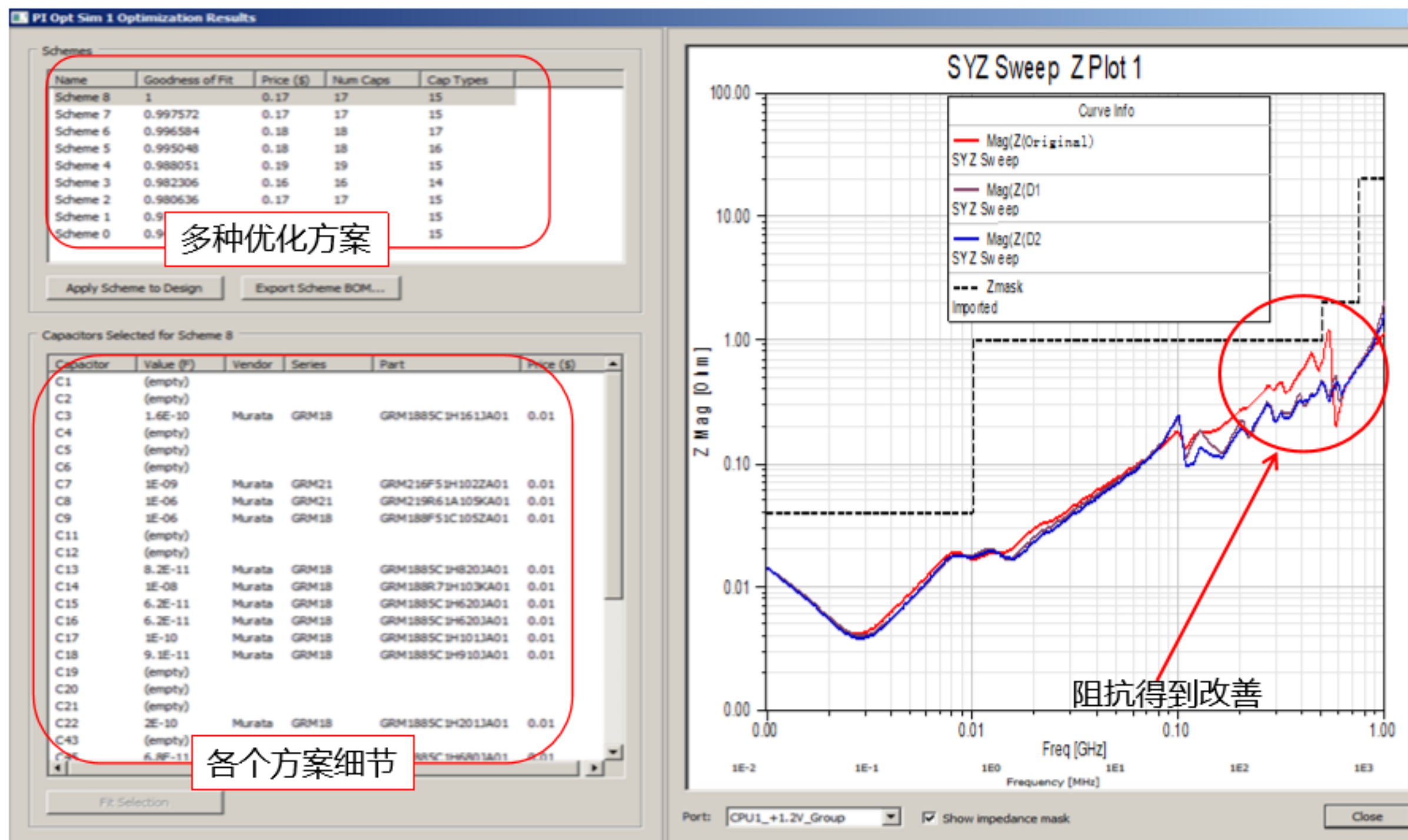
PCB电源噪声干扰案例



近场辐射分布

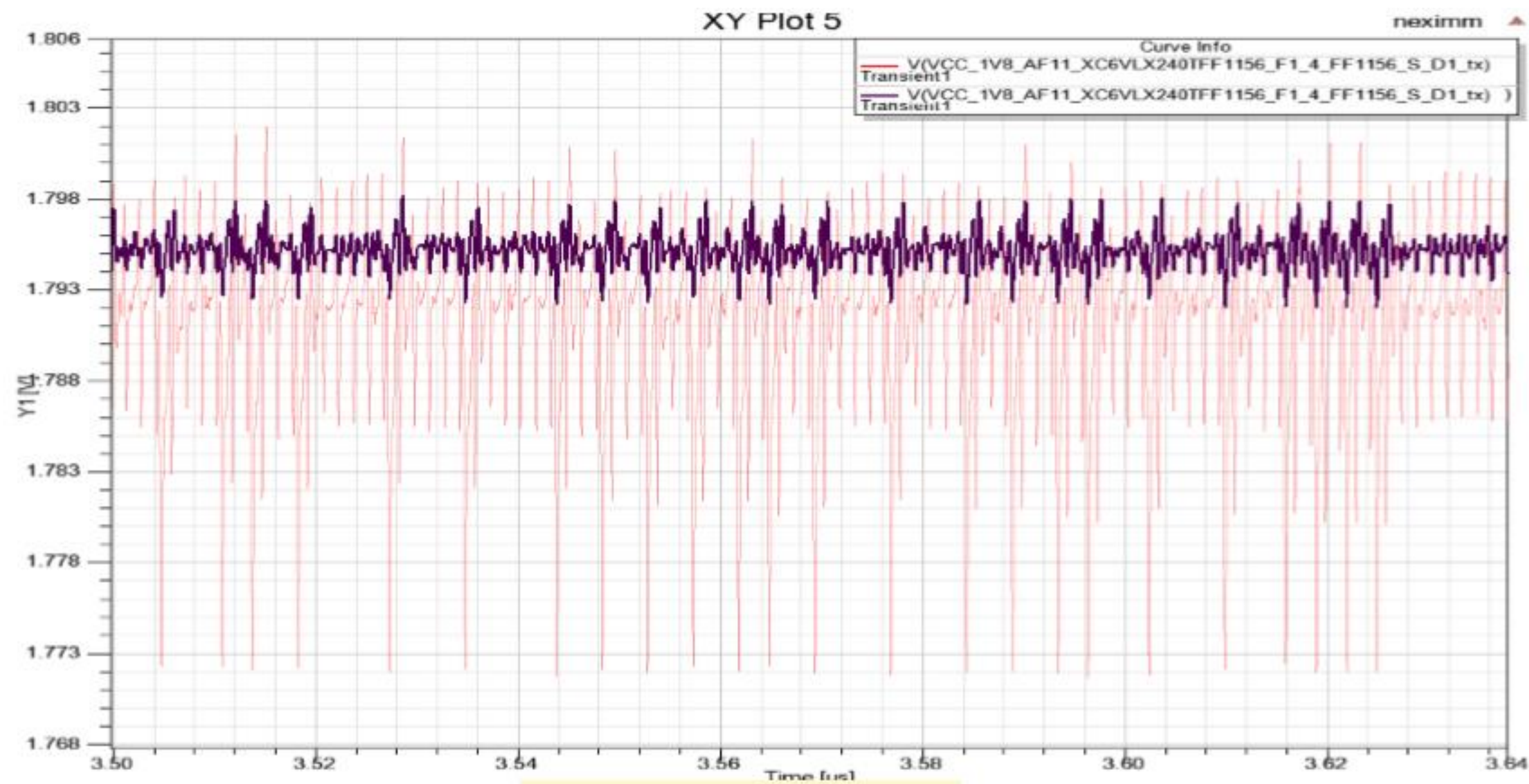
PCB电源噪声干扰案例

电源平面目标阻抗优化结果



PCB电源噪声干扰案例

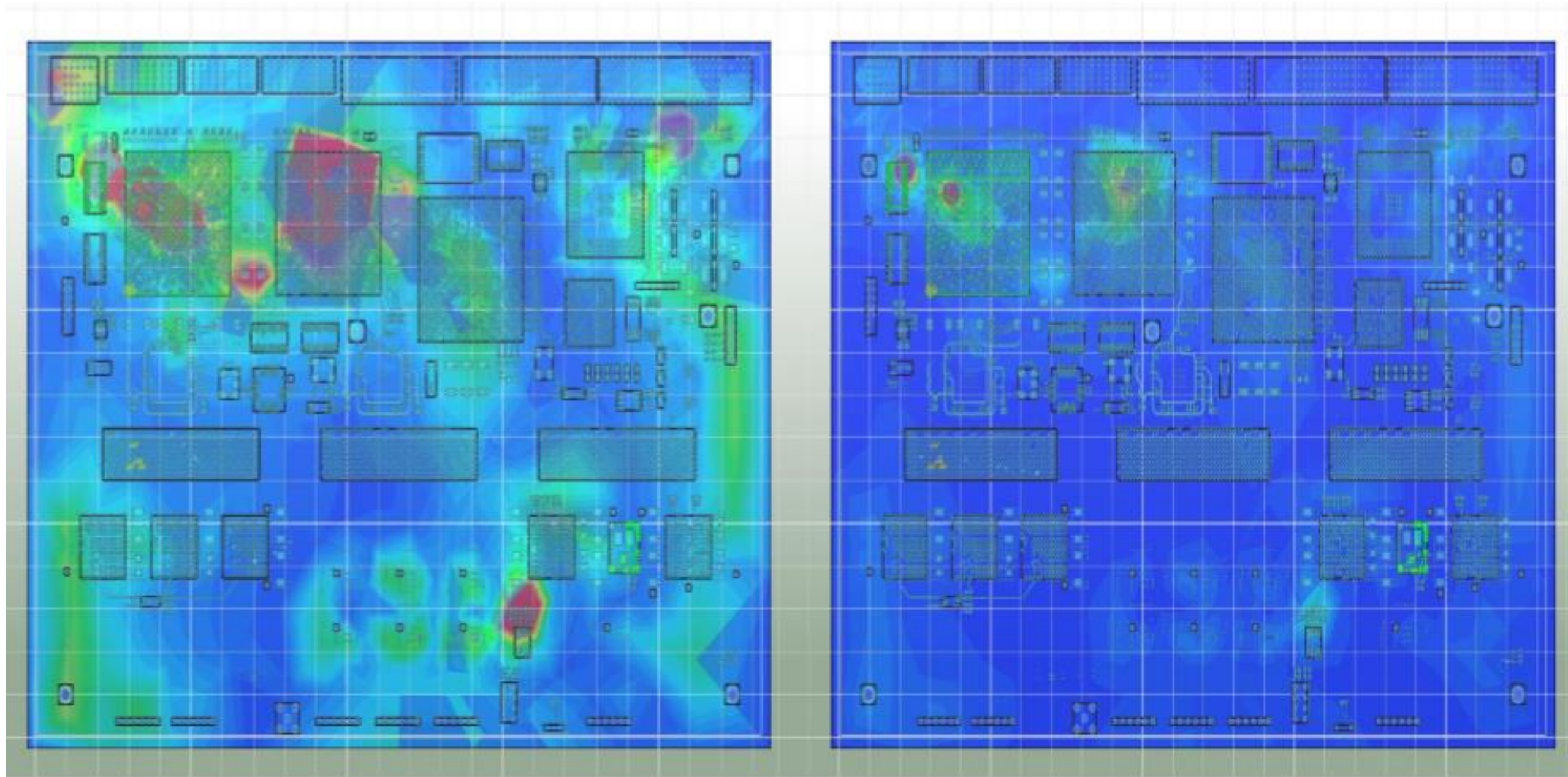
电源时域抖动改善



电源波动-优化前后对比

PCB电源噪声干扰案例

PCB近场优化对比



PCB电源优化前

PCB电源优化后

目录

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2. SIwave功能介绍
3. 新版本新功能

ANSYS SIwave

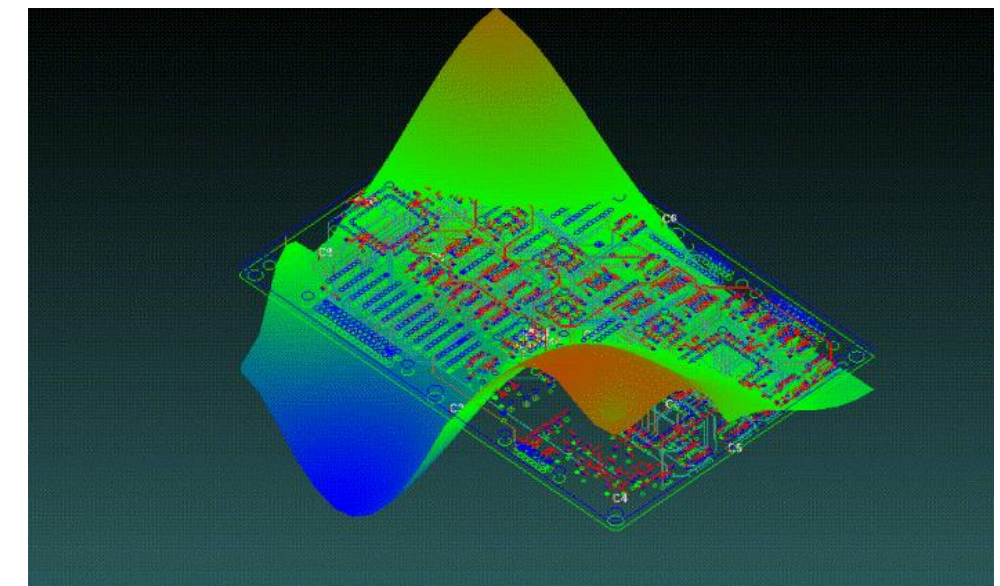
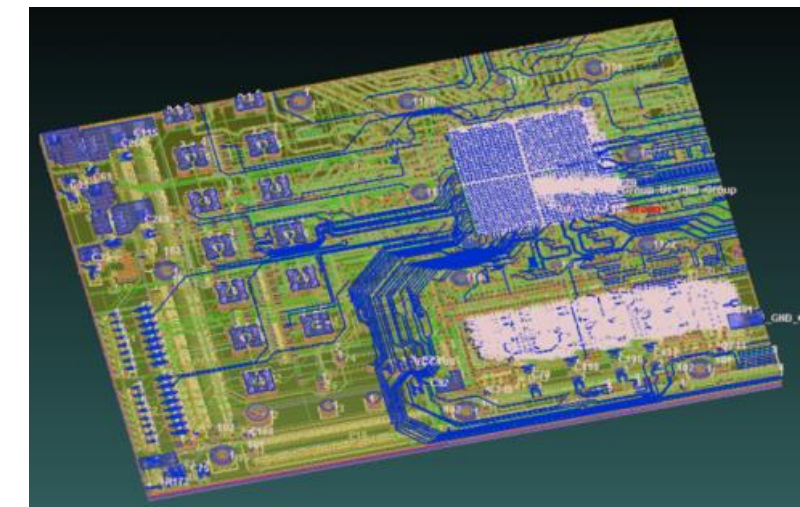
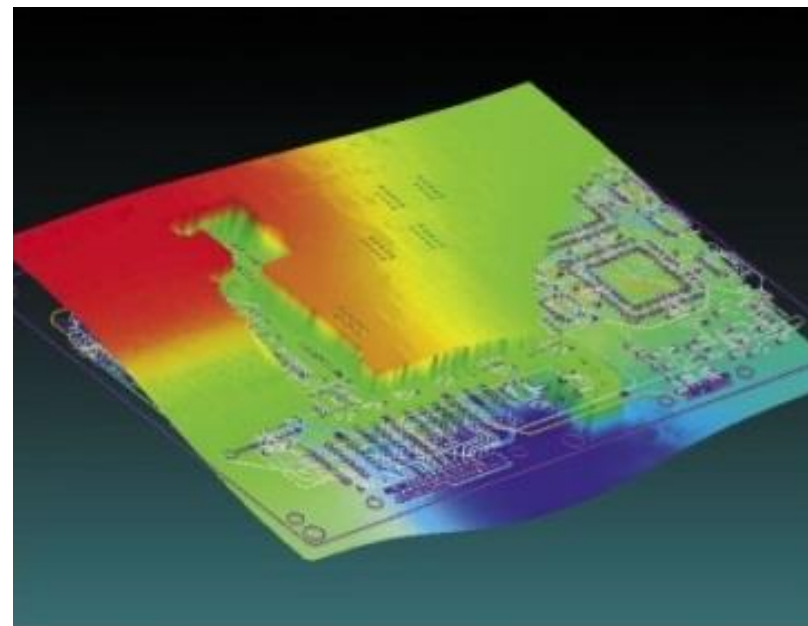
SIwave是特别针对**PCB、芯片封装的SI/PI/EMC仿真工具**，采用定制化的电磁场算法, 能够高效准确地求解几十层的PCB和上千管脚的封装结构。

功能特点

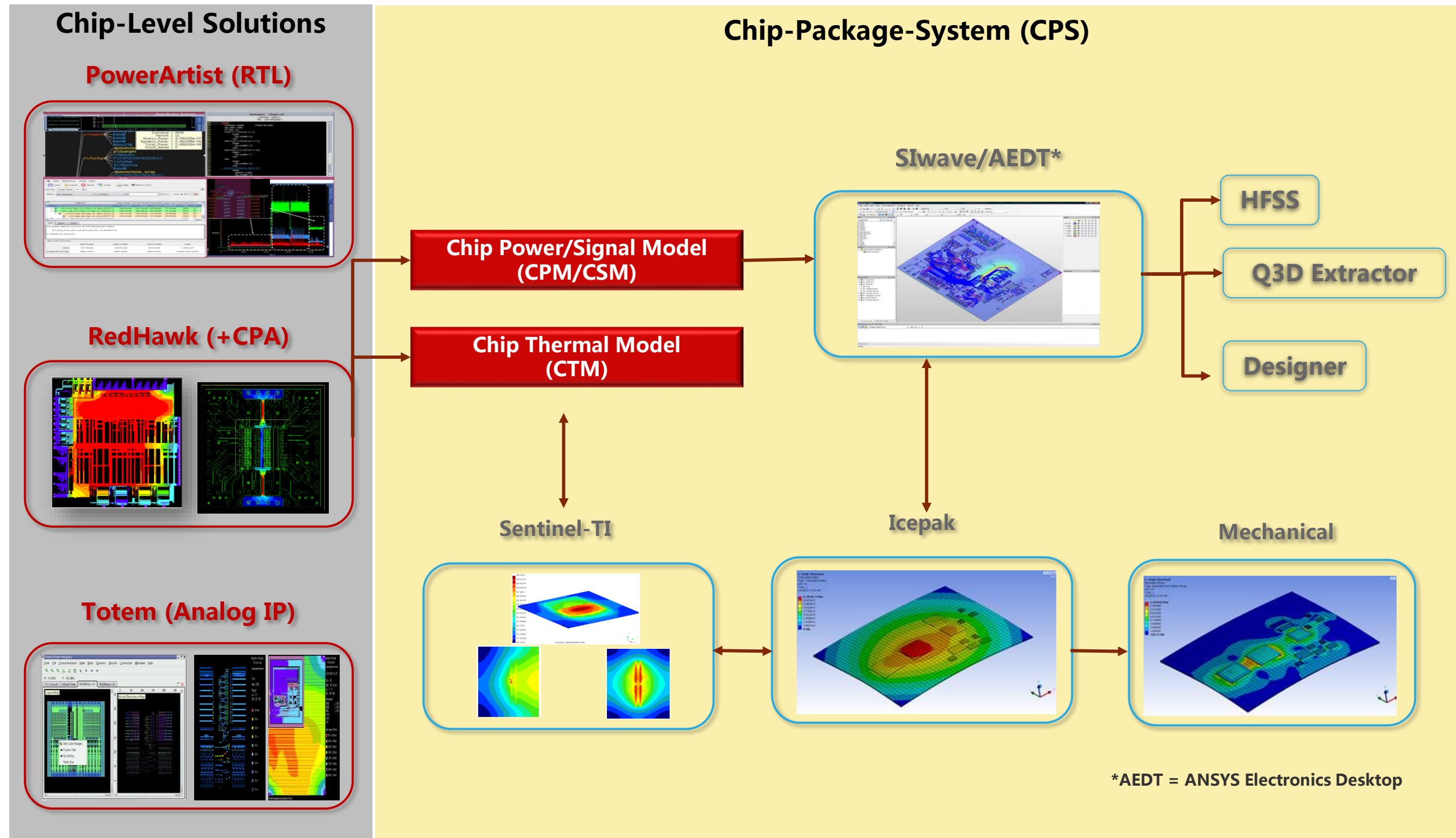
- 与EDA设计工具无缝集成
- 涵盖PCB从直流设计到去耦电容设计，从高速设计到EMC设计所有方面
- 帮助工程师深刻洞察电路器件与电磁场器件的相互作用
- 自动考虑PCB板上所有互连结构，如走线、过孔和焊盘等

应用领域

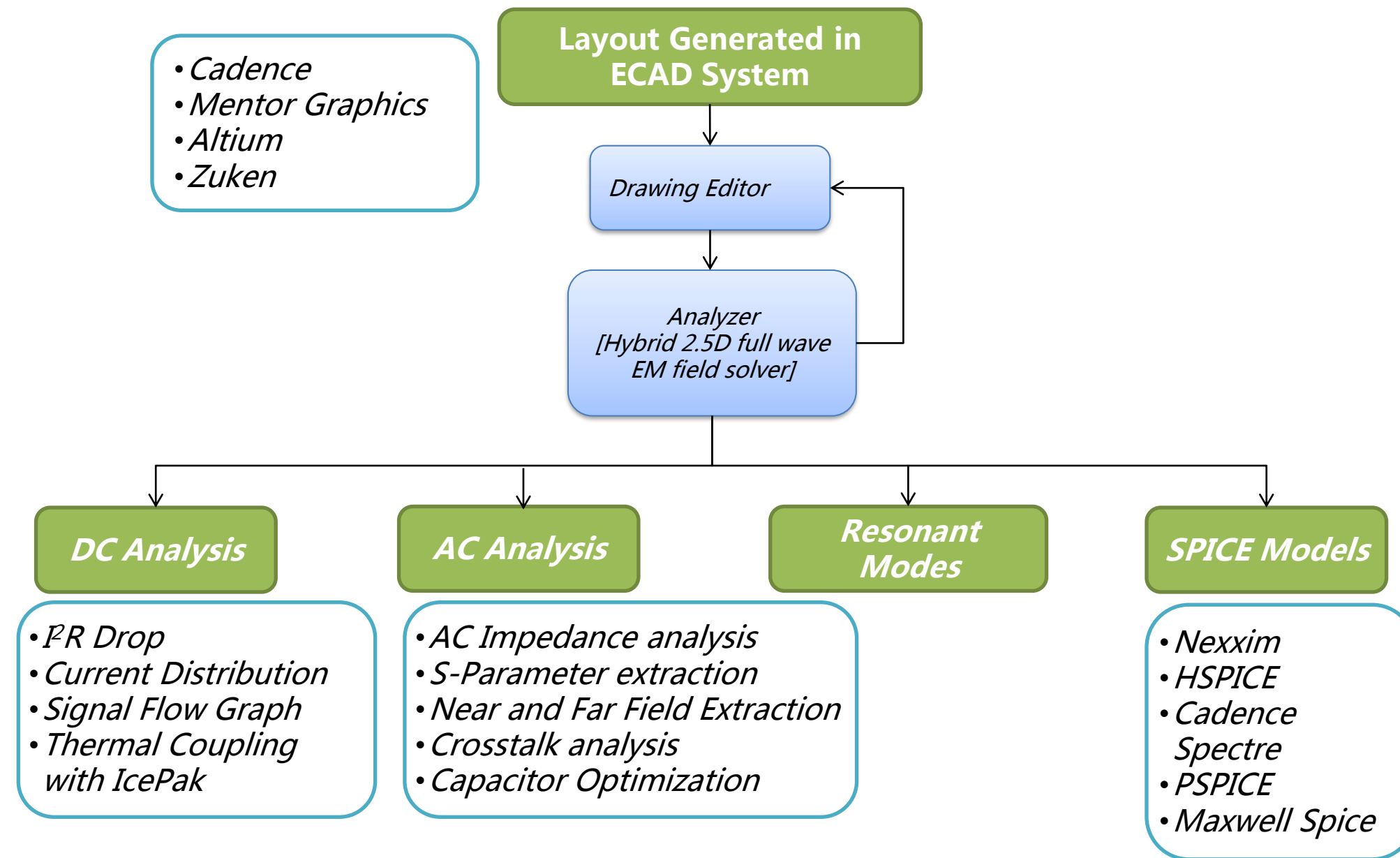
- 集成电路 (IC) 封装
- PCB 直流分布、SI、PI
- 去耦电容自动优化
- 高速通道设计
- 近远场辐射、EMI/EMC



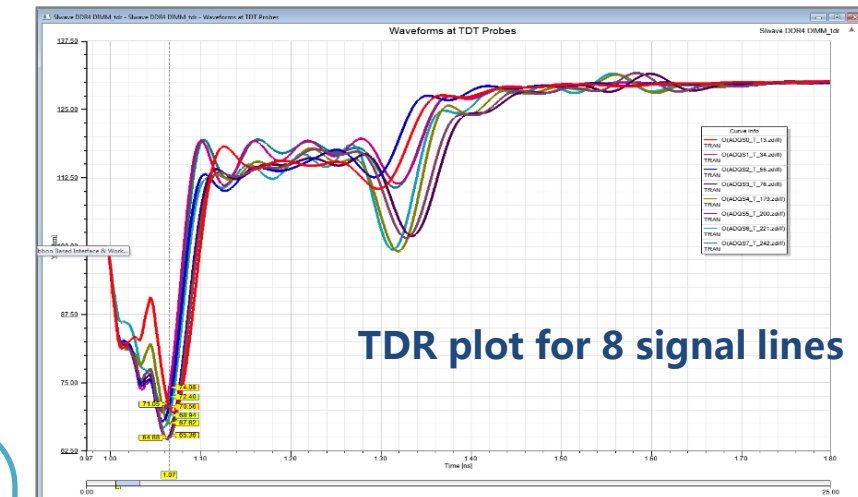
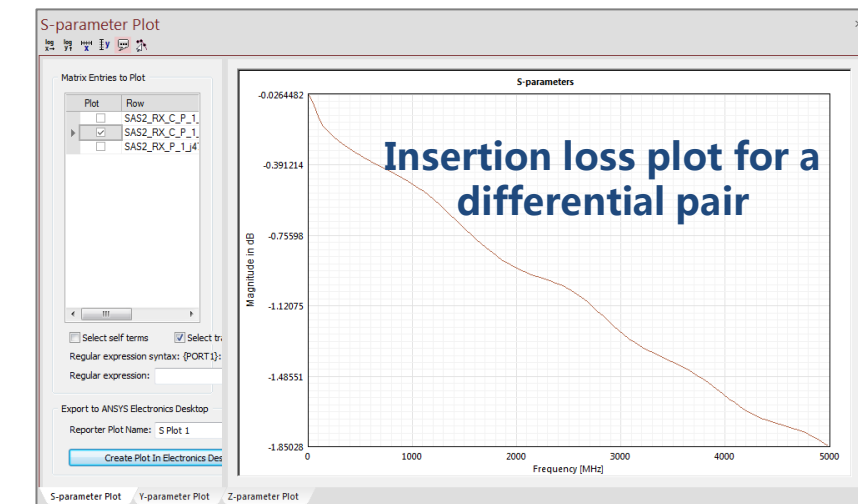
ANSYS Chip-Package-System Solutions



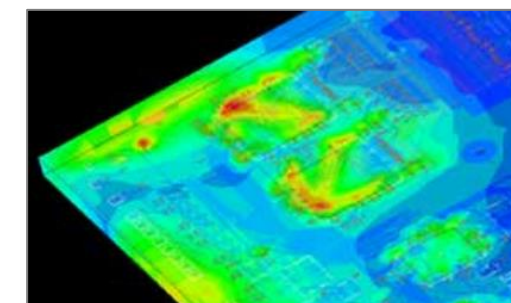
ANSYS SIwave



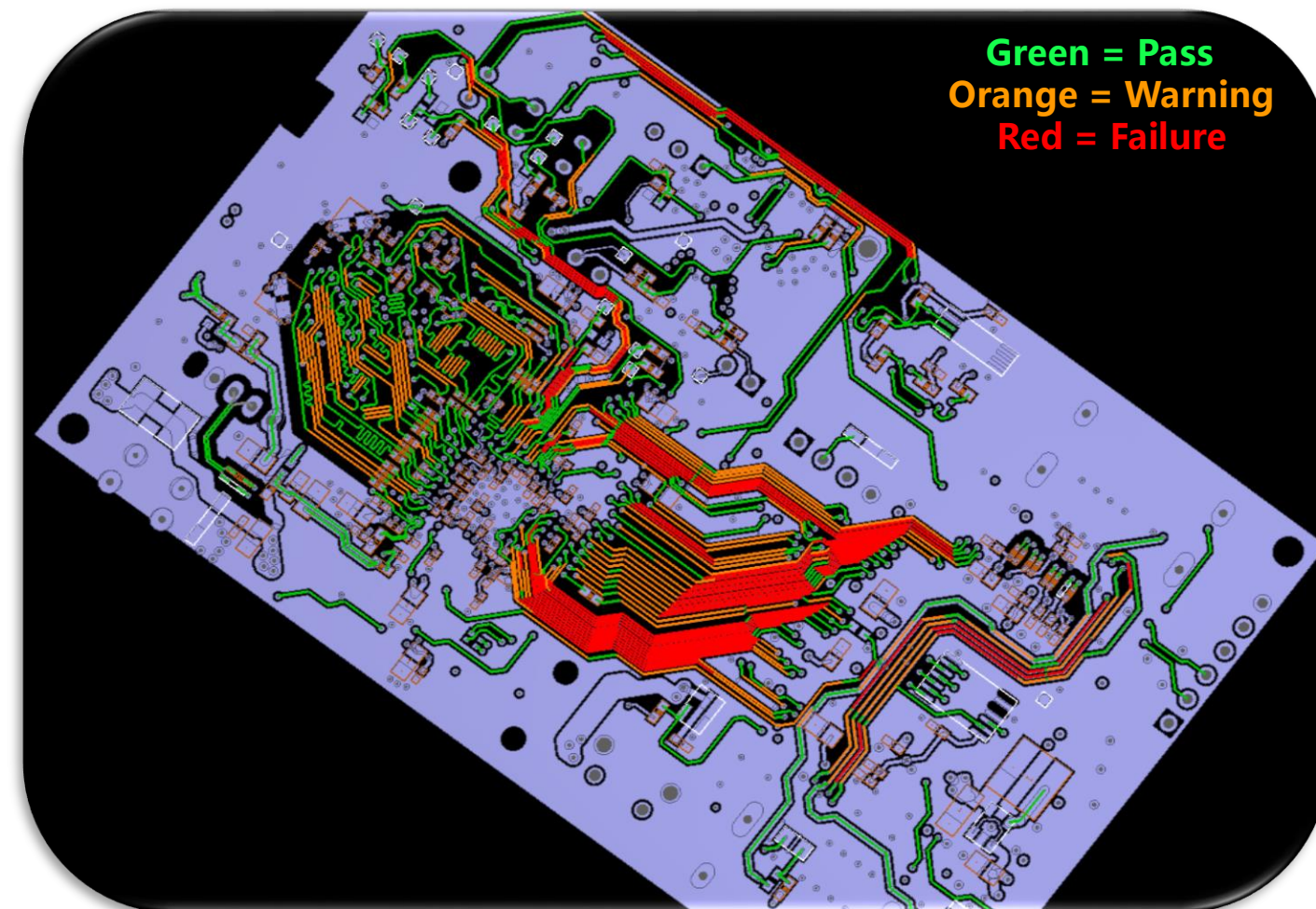
Hybrid solver technology enables simulation of entire system (PCB and Package)



Prediction of EMI on a dual-processor quad-core PCB. Plot depicts near-field magnetic field at 778 MHz



ANSYS SIwave——Layout Scanning

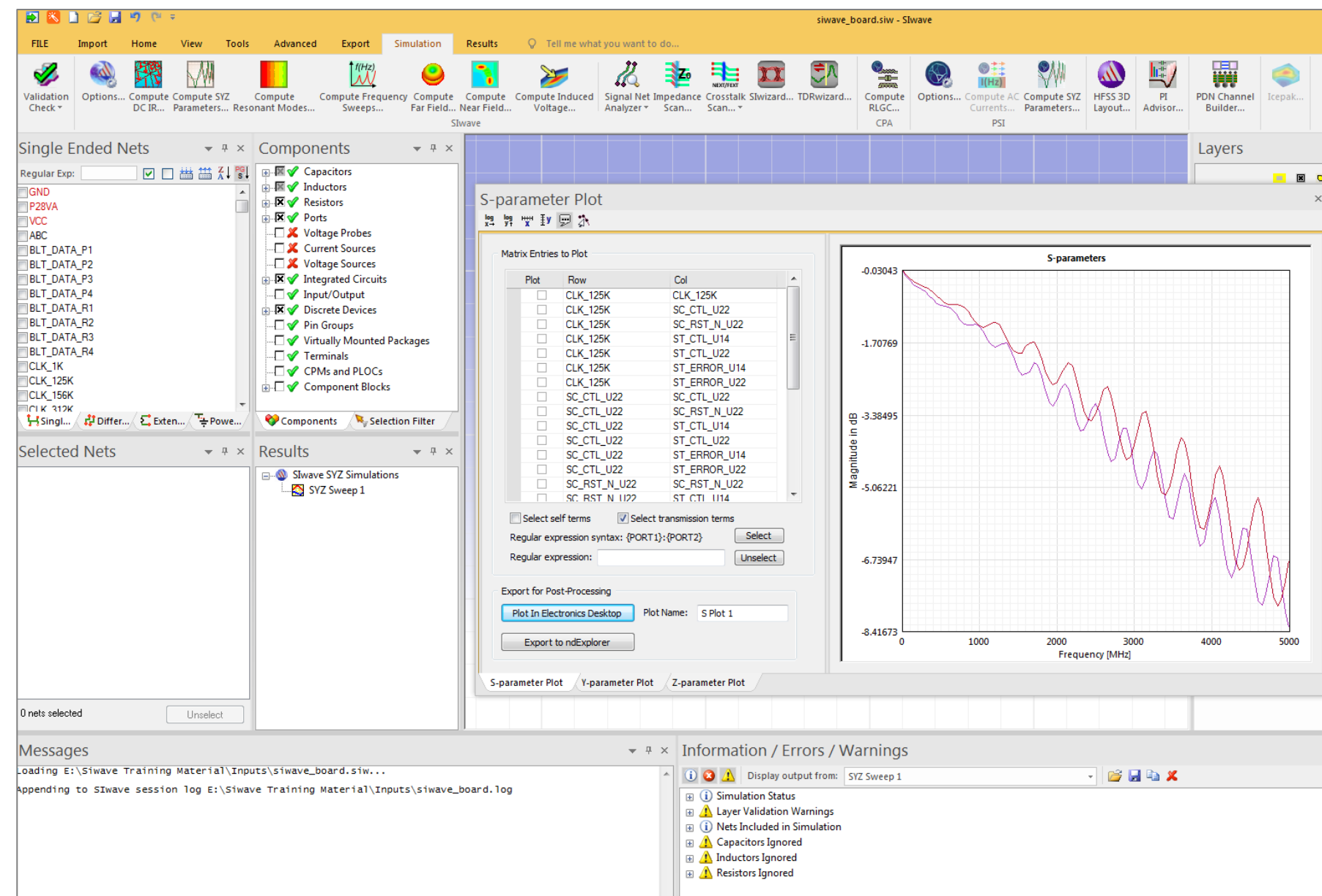
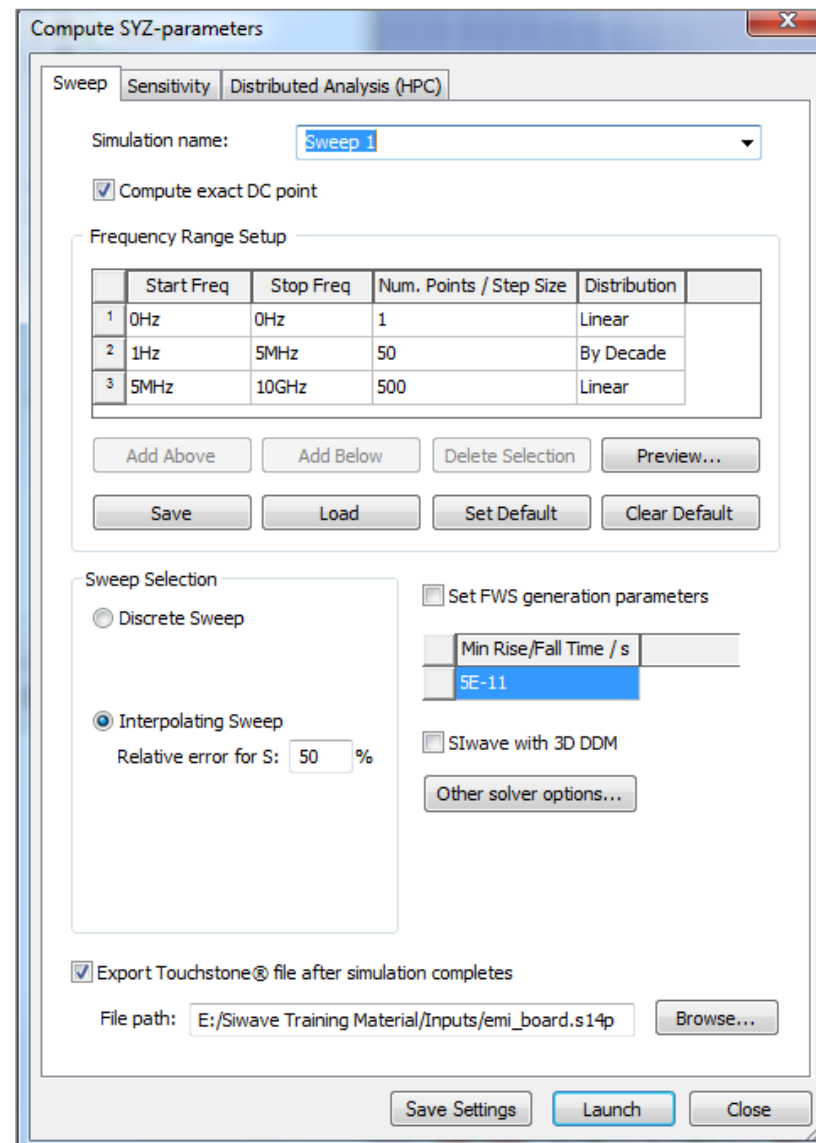
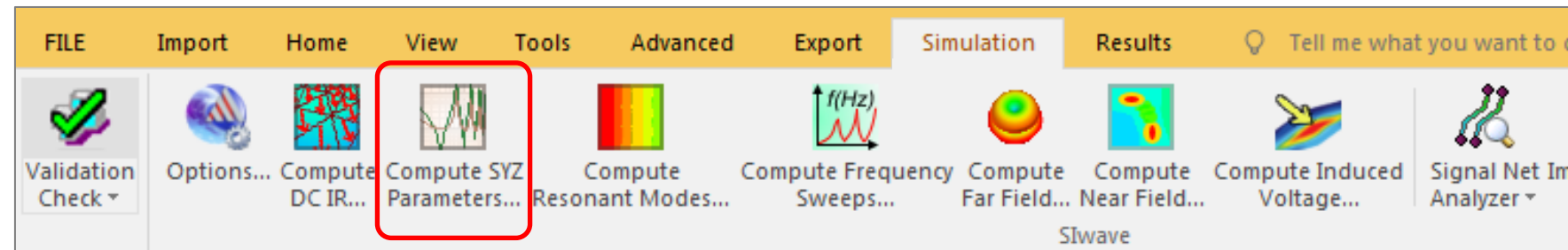


Net Name	NEXT Warning Tolerance	NEXT Violation Tolerance	SE or Diff	Cross Section Type	Violation	Layer of Violation	Max NEXT	Length of Max NEXT (mm)	NEXT of Longest Line Section	Length of Longest Line Section (mm)
VSYNC_5TB	0.1	0.2	SE	MSL; STL	No		0.06	2.071	0.024	8.644
V_HDMI_5V	0.1	0.2	SE	MSL; STL	No		0.044	2.52	0	11.009
XMMCCLK0	0.1	0.2	SE	MSL; STL	No		0.1	1.295	0.031	14.542
XMMCCMD0	0.1	0.2	SE	MSL; STL	No		0.1	1.854	0.066	9.626
XMMCDATA0_0	0.1	0.2	SE	MSL; STL	No		0.099	3.128	0.078	18
XMMCDATA0_1	0.1	0.2	SE	MSL; STL	No		0.098	3.033	0.035	14.573
XMMCDATA0_2	0.1	0.2	SE	MSL; STL	No		0.1	1.295	0.031	14.542
XMMCDATA0_3	0.1	0.2	SE	MSL; STL	No		0.097	8.941	0.031	14.549
XNRESET	0.1	0.2	SE	MSL; STL	No		0.099	5.984	0.016	23.085
XOTGD	0.1	0.2	Diff	MSL; STL	No		0.001	7.57	0	8.027
XOTGD_EMI	0.1	0.2	Diff	MSL; STL	No		0	1.85	0	1.85
XOTGID	0.1	0.2	SE	MSL; STL	No		0.011	1.278	0	9.888
XURXD_0	0.1	0.2	SE	MSL; STL	No		0.084	1.47	0	7.186
XUSBHD	0.1	0.2	Diff	MSL; STL	No		0	6.116	0	6.116
XUTXD_0	0.1	0.2	SE	MSL; STL	No		0.083	2.842	0	7.687
XVBUS	0.1	0.2	SE	MSL; STL	No		0	7.793	0	7.793

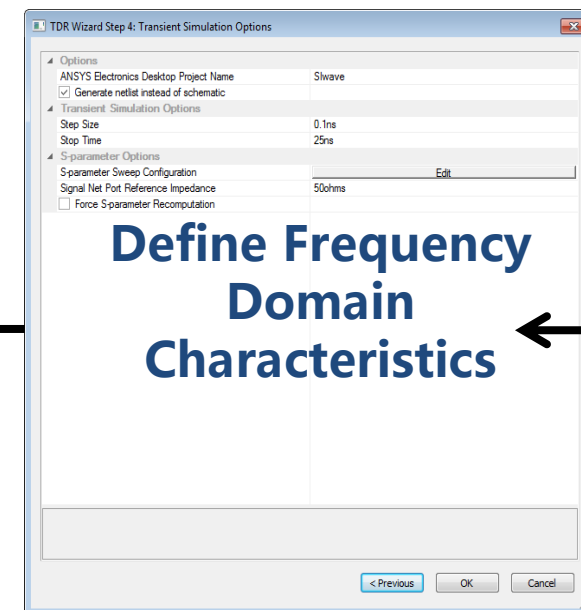
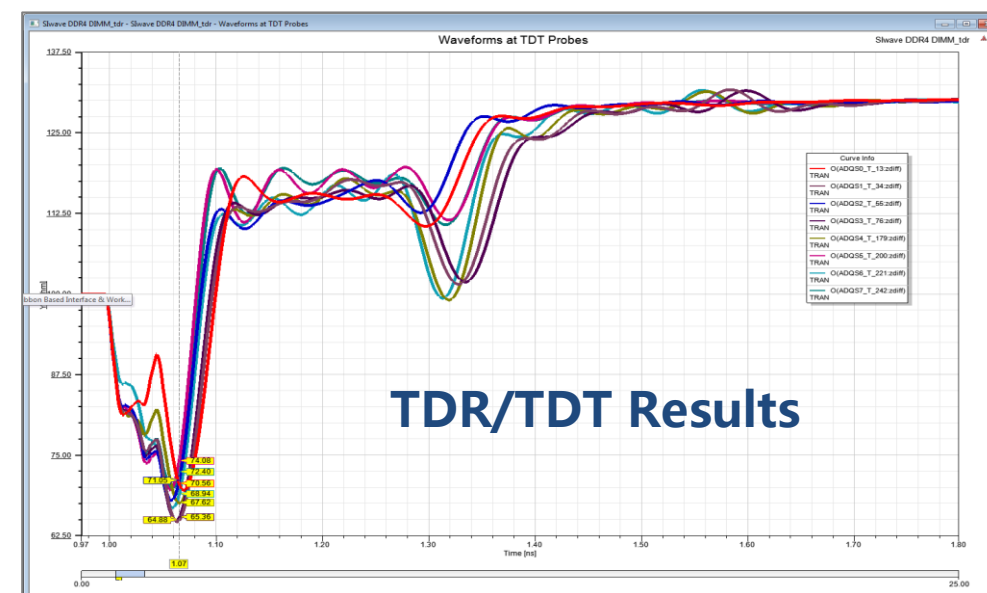
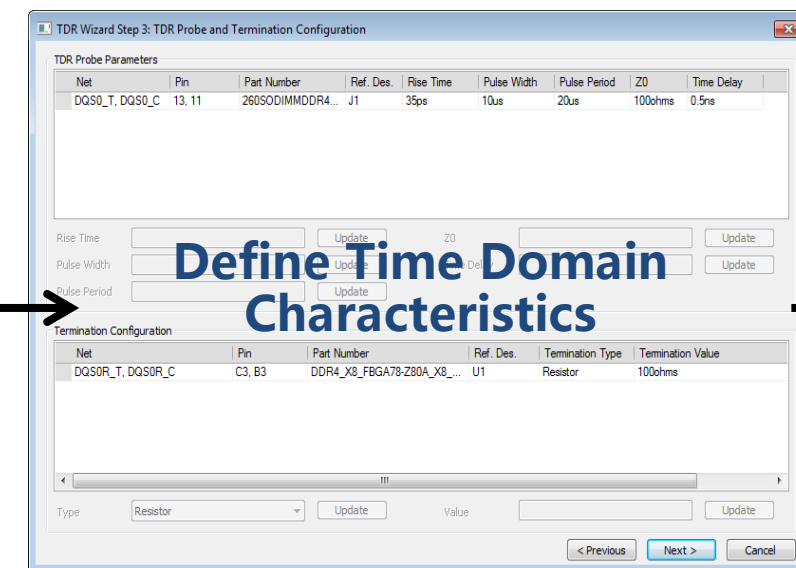
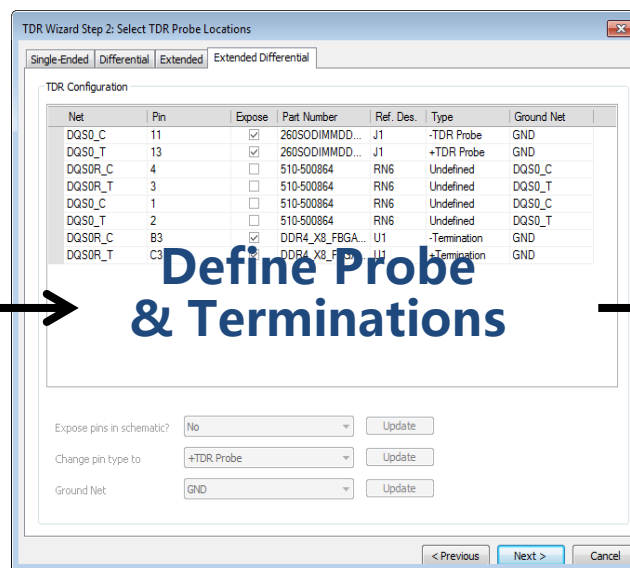
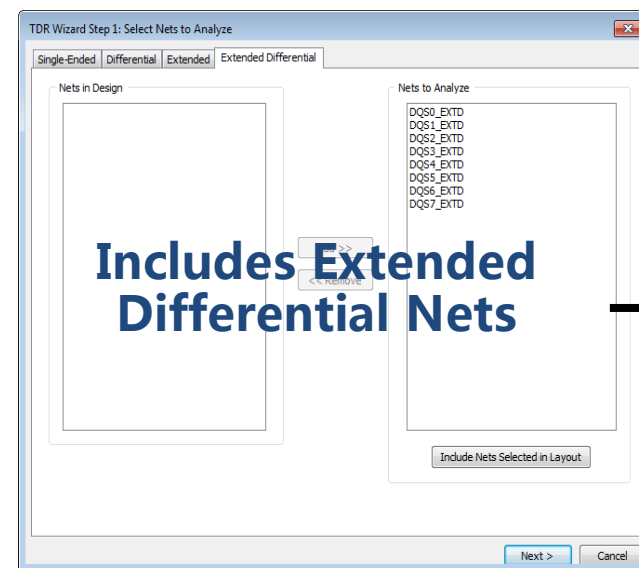
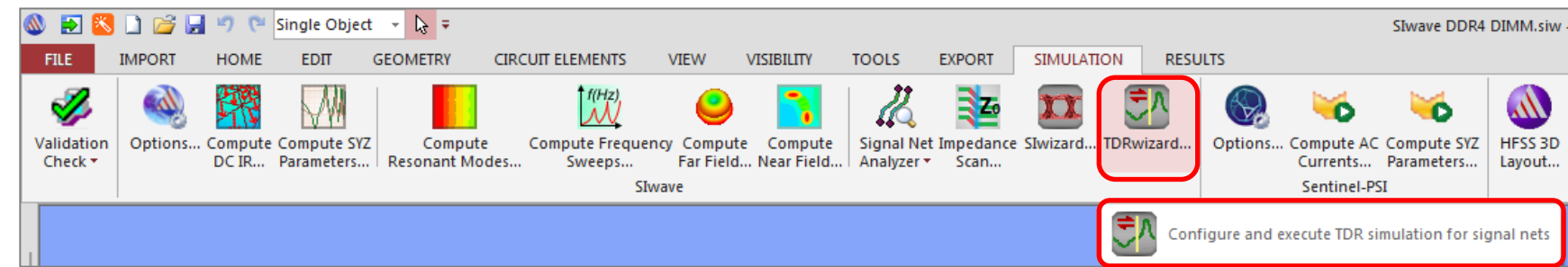
Net Name	FEXT Warning Tolerance (ns/m)	FEXT Violation Tolerance (ns/m)	SE or Diff	Cross Section Type	Violation	Layer of Violation	Max FEXT (ns/m)	Length of Max FEXT (mm)	FEXT of Longest Line Section (ns/m)	Length of Longest Line Section (mm)
						"top"	0.227	6.43	0.227	6.43
AP_TCK	0.1	0.2	SE	MSL; STL	Yes	"bottom"	0.205	3.268	0.205	3.268
AP_TDI	0.1	0.2	SE	MSL; STL	Yes	"bottom"	0.214	7.902	0.214	7.902
AP_TDO	0.1	0.2	SE	MSL; STL	Yes	"bottom"	0.219	4.037	0.204	8.152
						"top"	0.209	12.456	0.209	12.456
AP_TMS	0.1	0.2	SE	MSL; STL	Yes	"bottom"	0.205	1.425	0.205	1.425
AP_TRST	0.1	0.2	SE	MSL; STL	Yes	"bottom"	0.218	1.767	0.202	7.228
CEC	0.1	0.2	SE	MSL; STL	Yes	"bottom"	0.203	8.142	0.203	8.142

Full PCB Zo and NEXT/FEXT Scanning Capabilities

ANSYS SIwave——S parameter



ANSYS SIwave——TDR



ANSYS SIwave—Time domain Simulation

Circuit Simulation using Nexxim

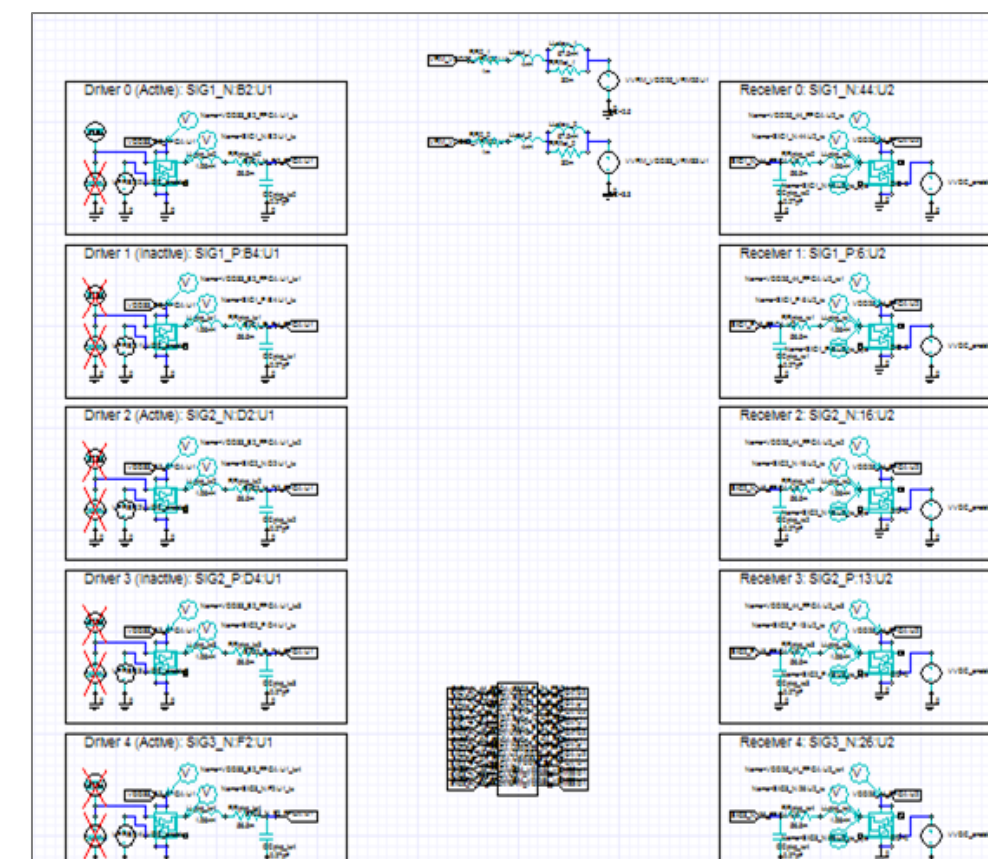
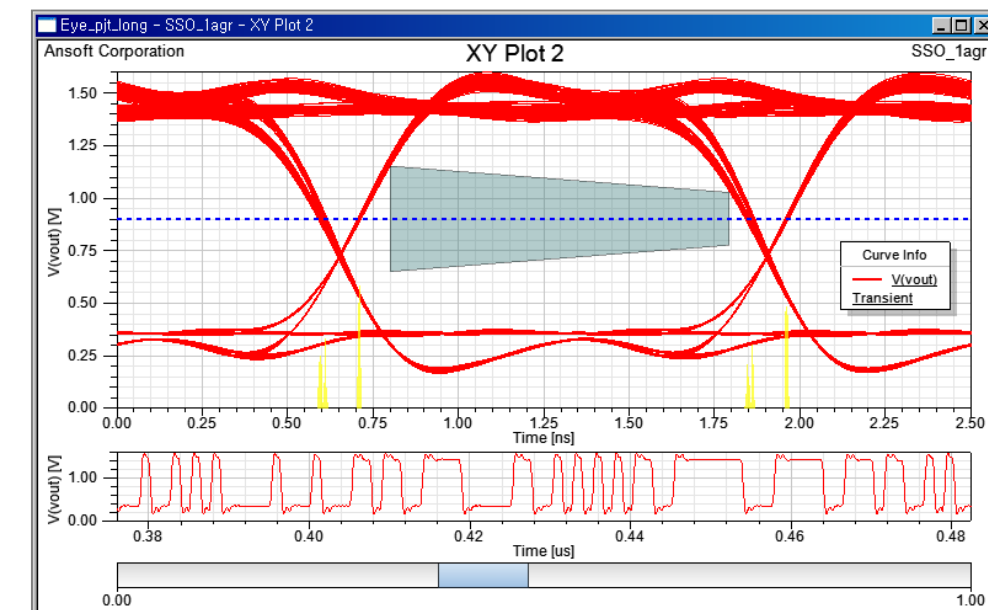
- Schematic entry GUI or Netlist entry (user choice)

Supports

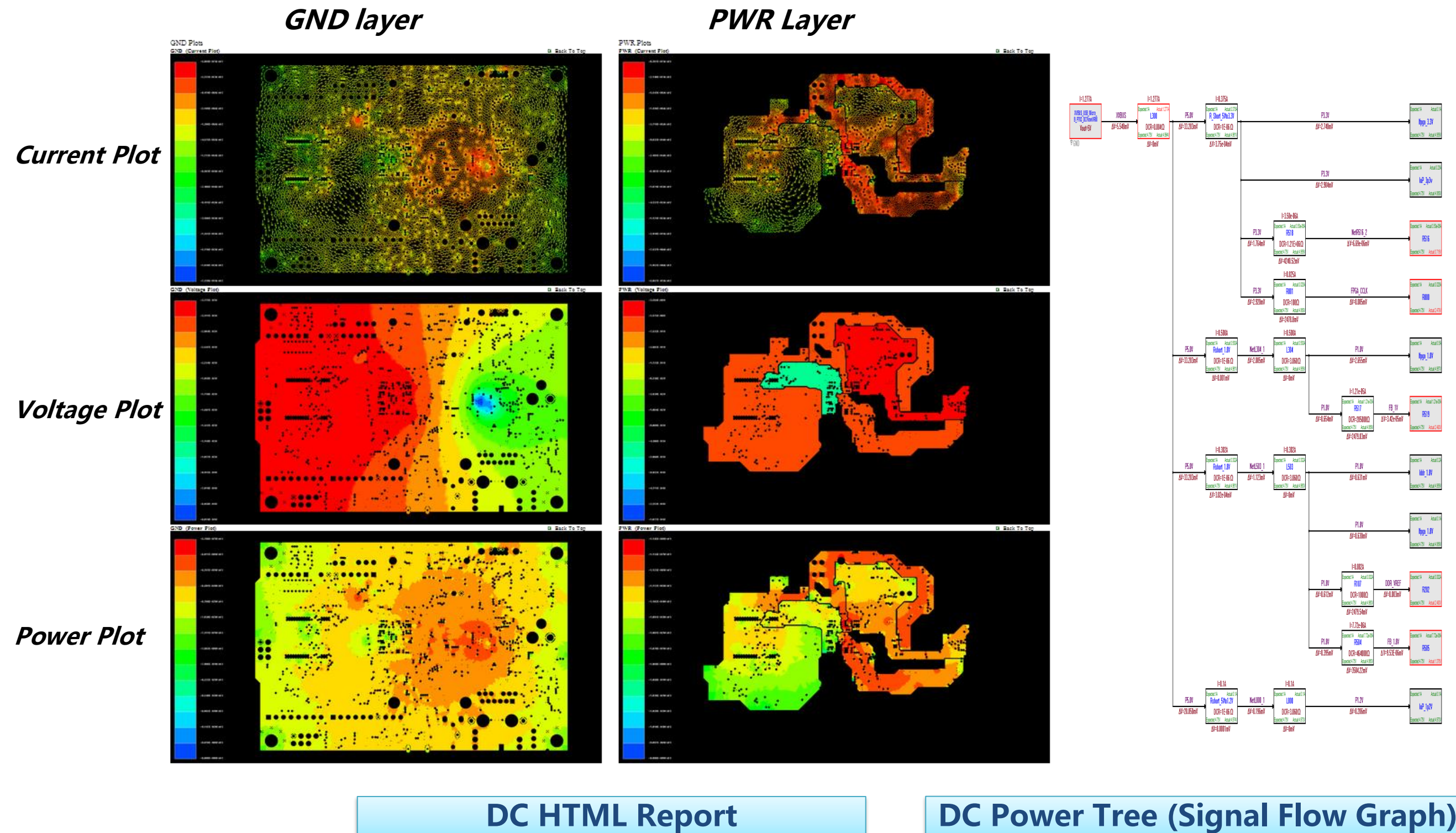
- HSPICE netlists, Spectre netlists, and Spectre RF netlists

Simulation Engines

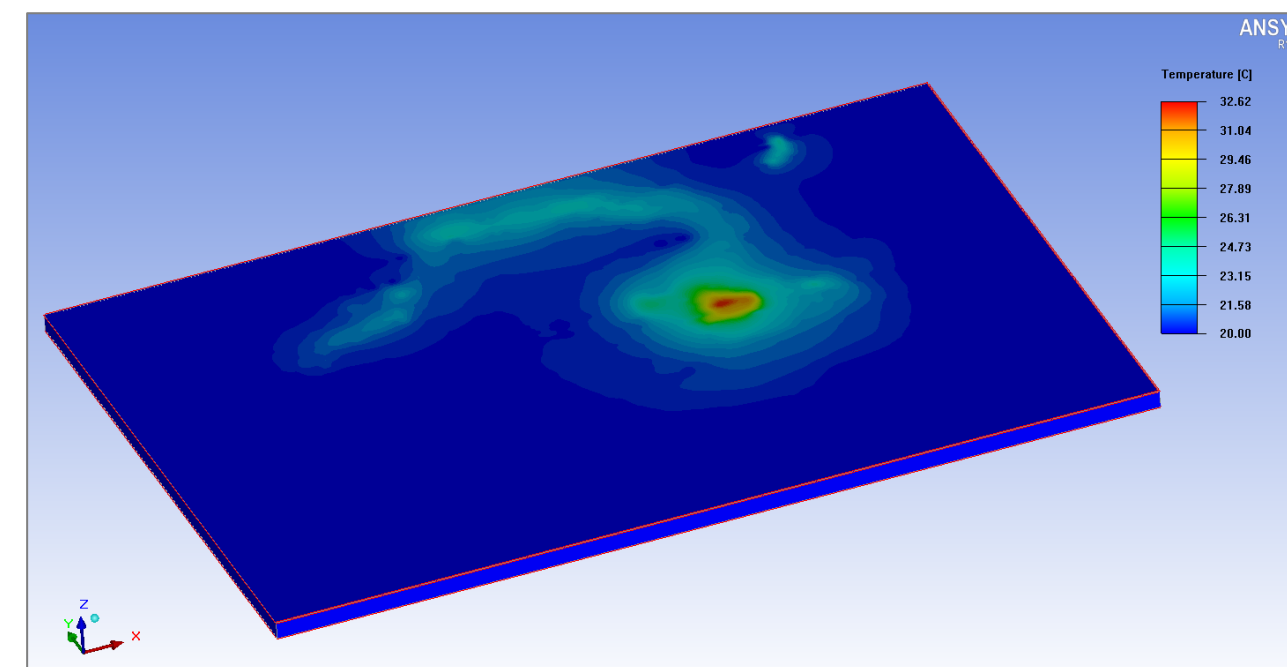
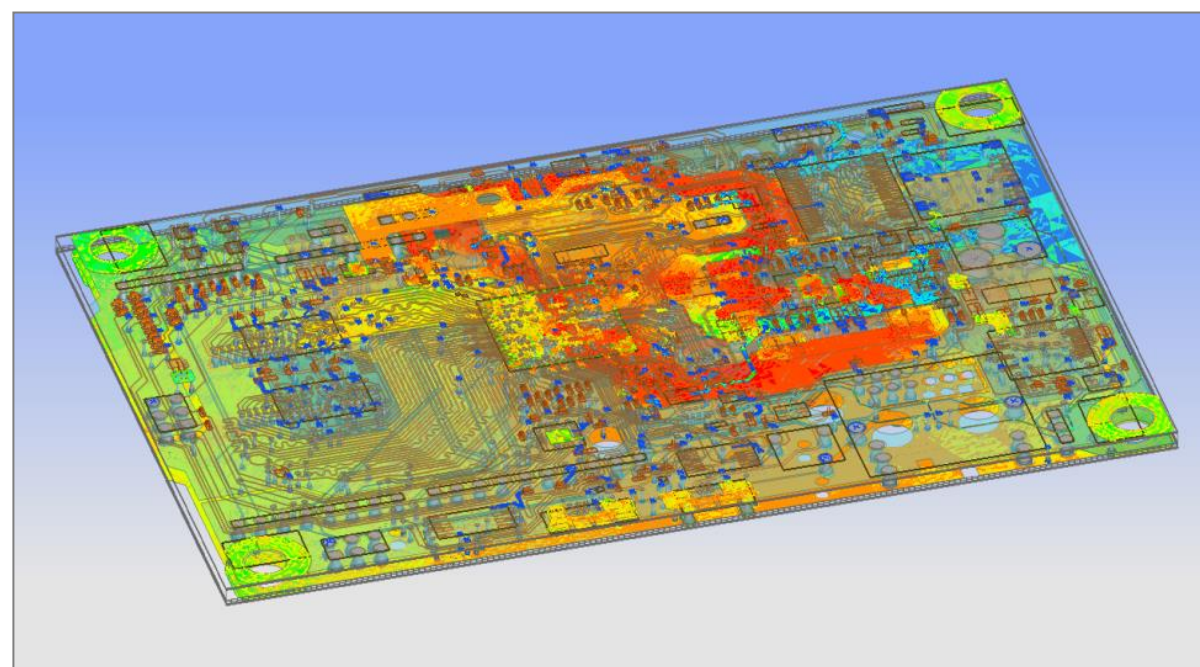
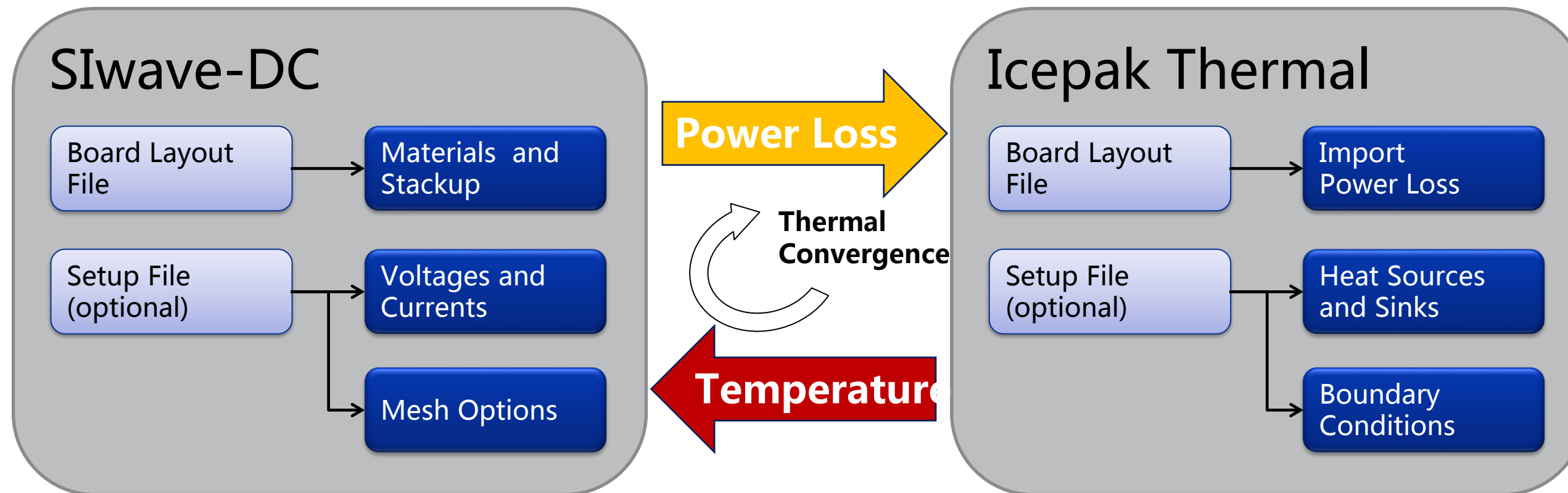
- Nexxim (SI focused analyses)
 - Linear network analysis (SYZ network analysis)
 - Causality checking and enforcement
 - Passivity checking and enforcement
 - TouchStone viewing and matrix reduction
- Traditional Transient
 - QuickEye (Convolution bit pattern based approach)
 - Including Peak Distortion Analysis (determines channel worst case bit pattern)
 - VerifEye (Statistical convolution approach)
 - Including 8b/10b with disparity algorithm



ANSYS SIwave——DC IR Drop Analysis

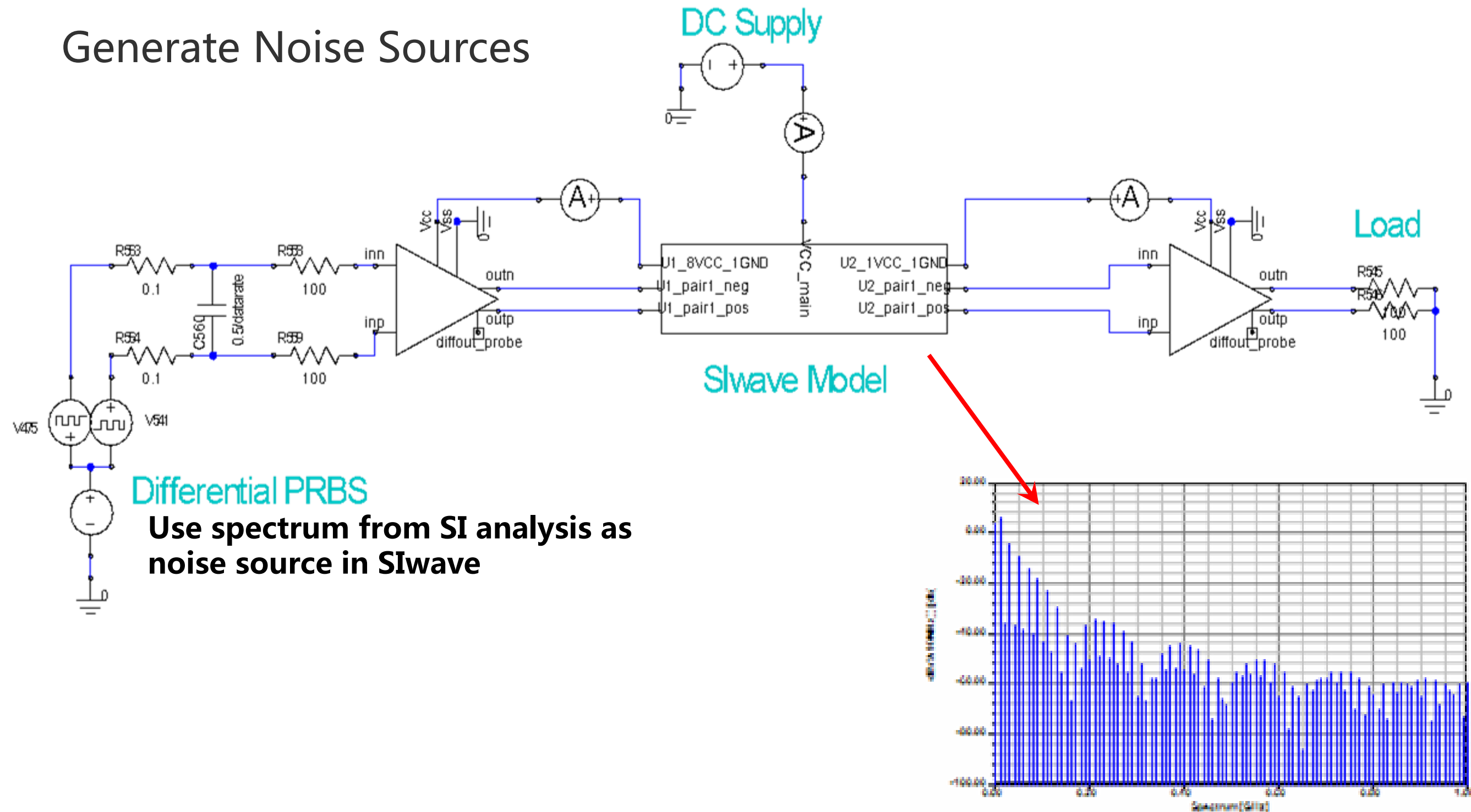


ANSYS SIwave—Bi-directional Thermal Coupling with Icepak



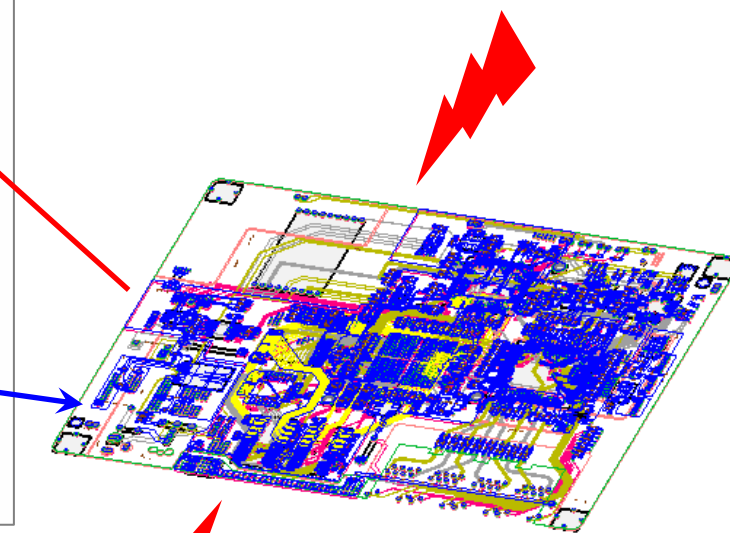
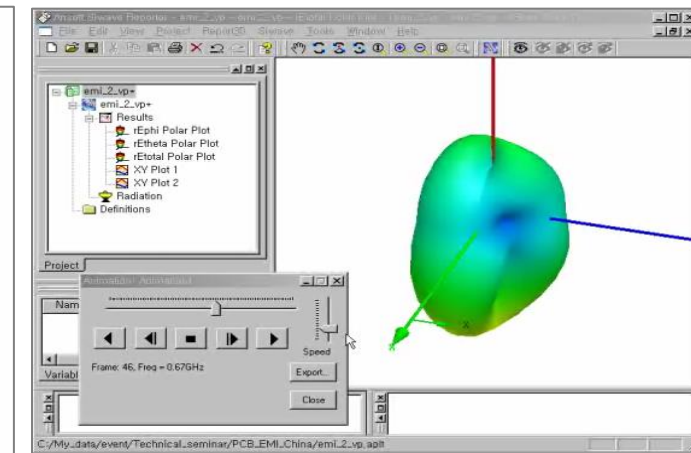
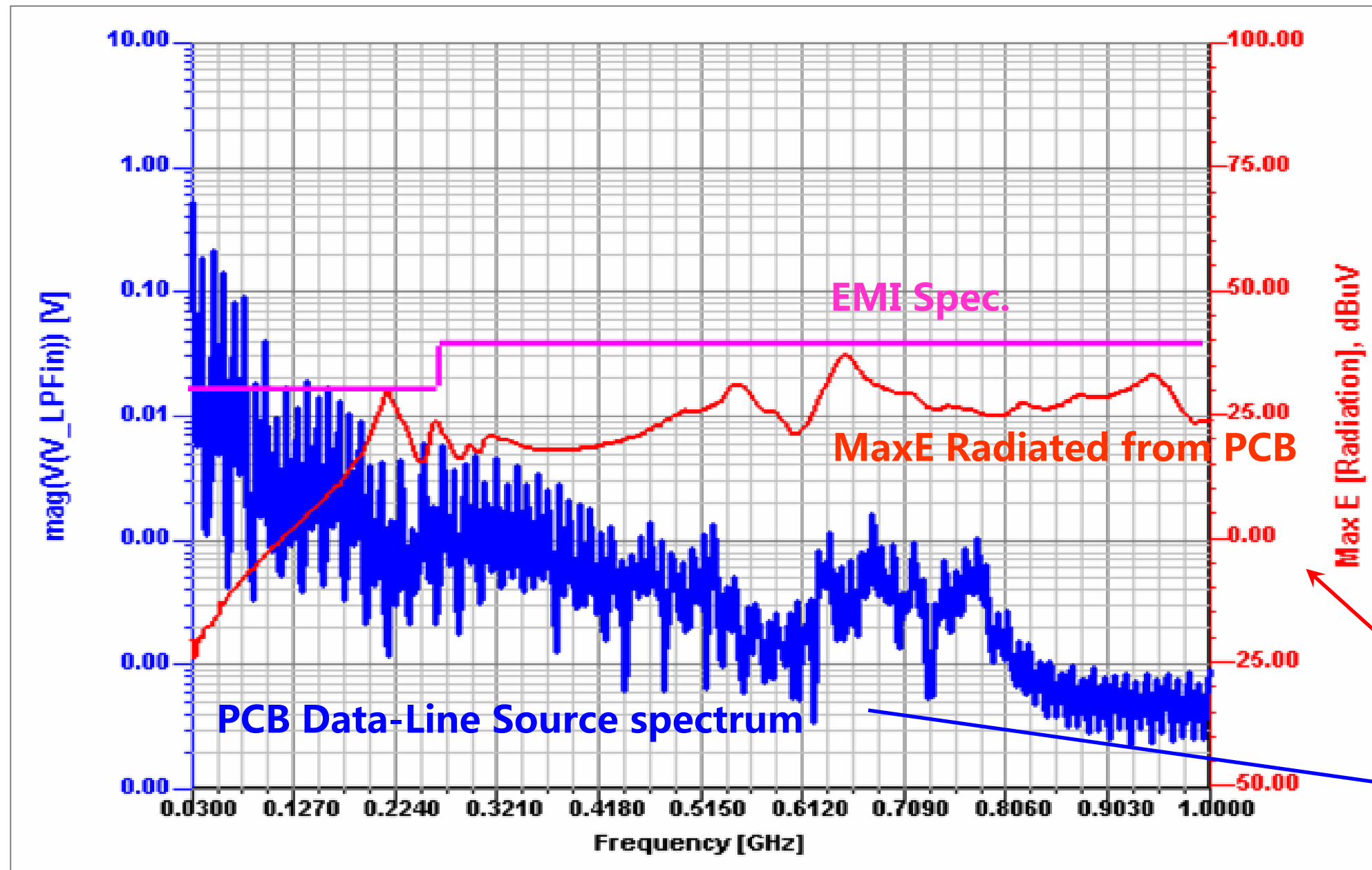
ANSYS SIwave—EMI/EMC

Generate Noise Sources



ANSYS SIwave—EMI/EMC

Plotting Far Fields



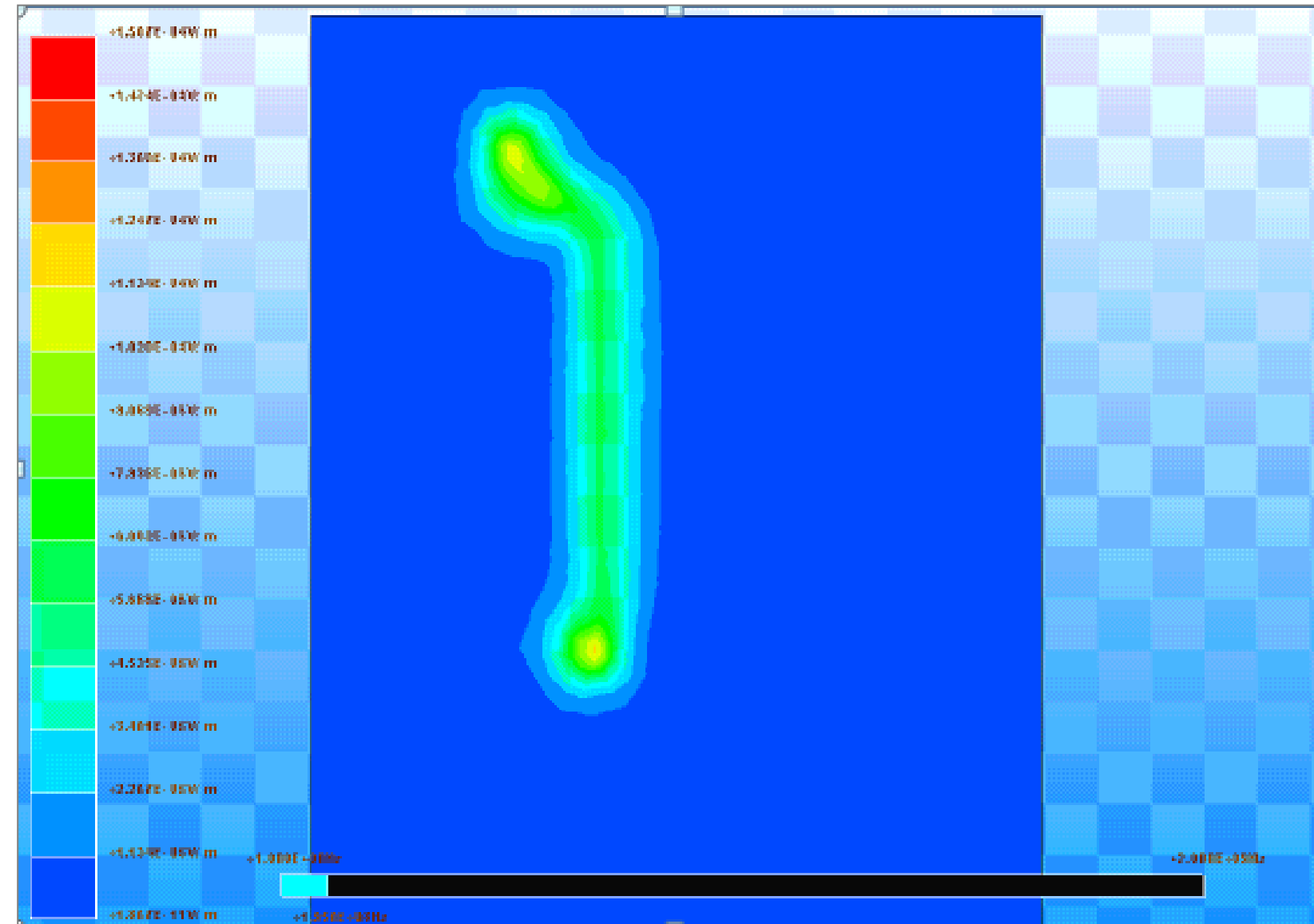
ANSYS SIMULATION ADVANTAGES:

- Fast and Accurate
- EMC Normative testing in few minutes
- No physical prototype and expensive anechoic chamber needed

SIwave

ANSYS SIwave——EMI/EMC

Near Field



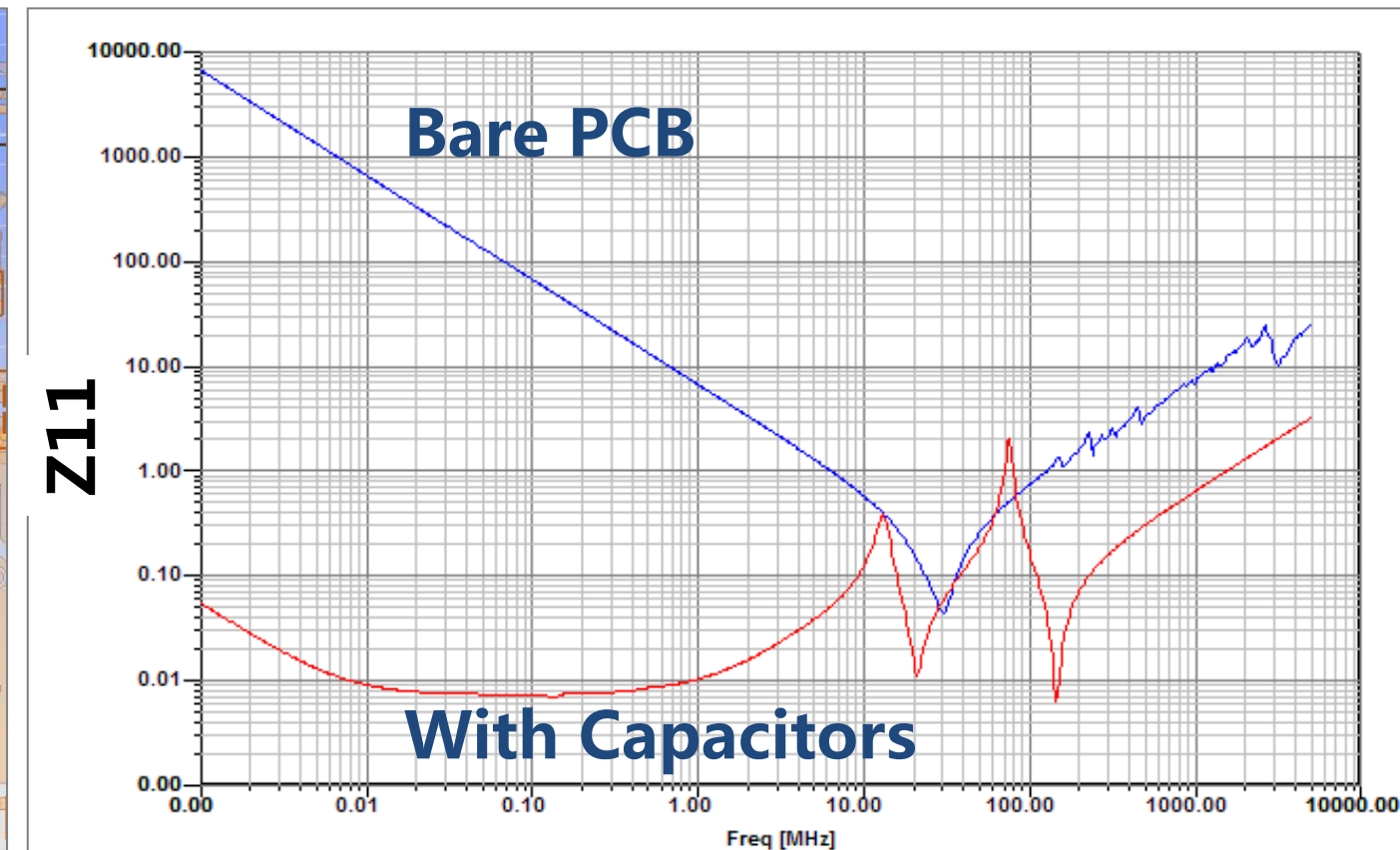
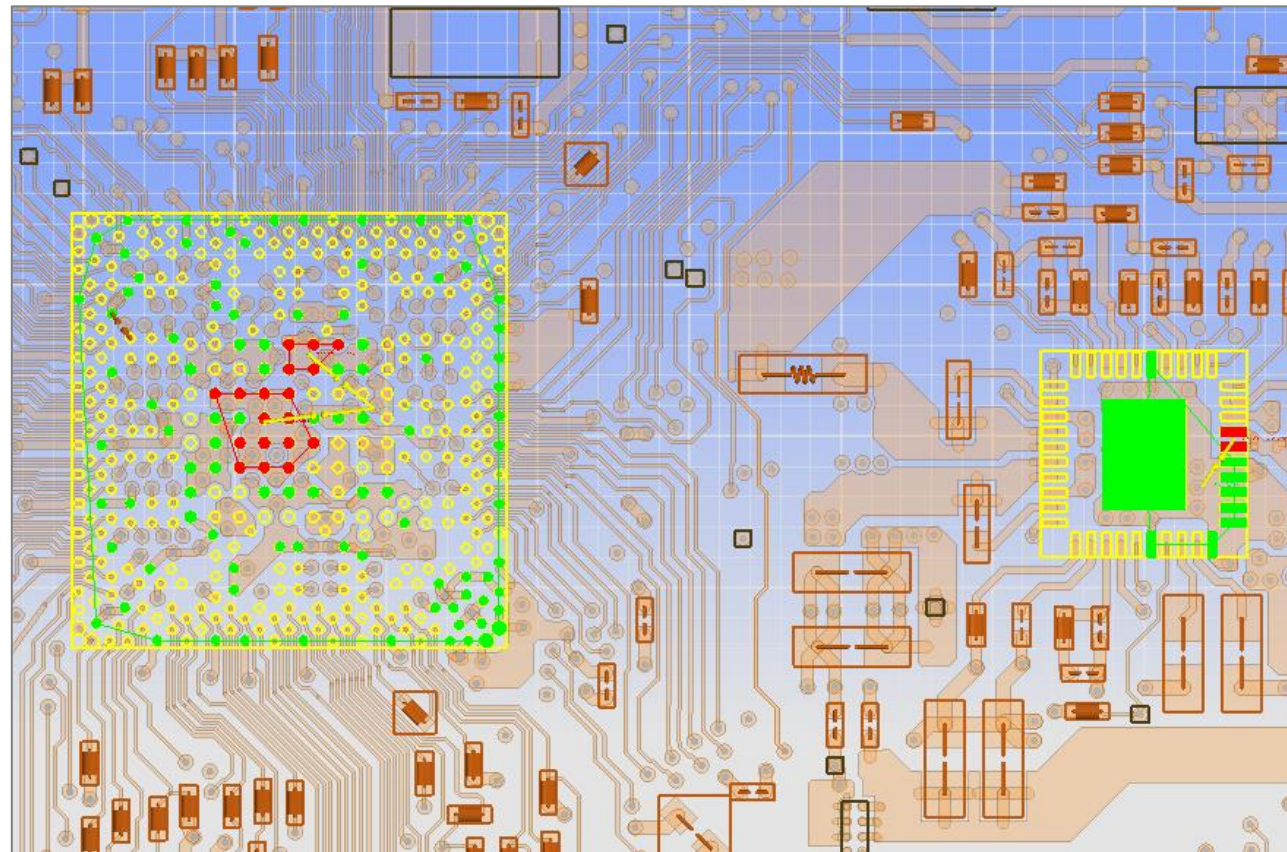
ANSYS SIMULATION ADVANTAGES:

- Fast and Accurate
- Recognize critical areas on the PCB
- No physical prototype and expensive anechoic chamber needed

ANSYS SIwave——Power Delivery Network Impedance

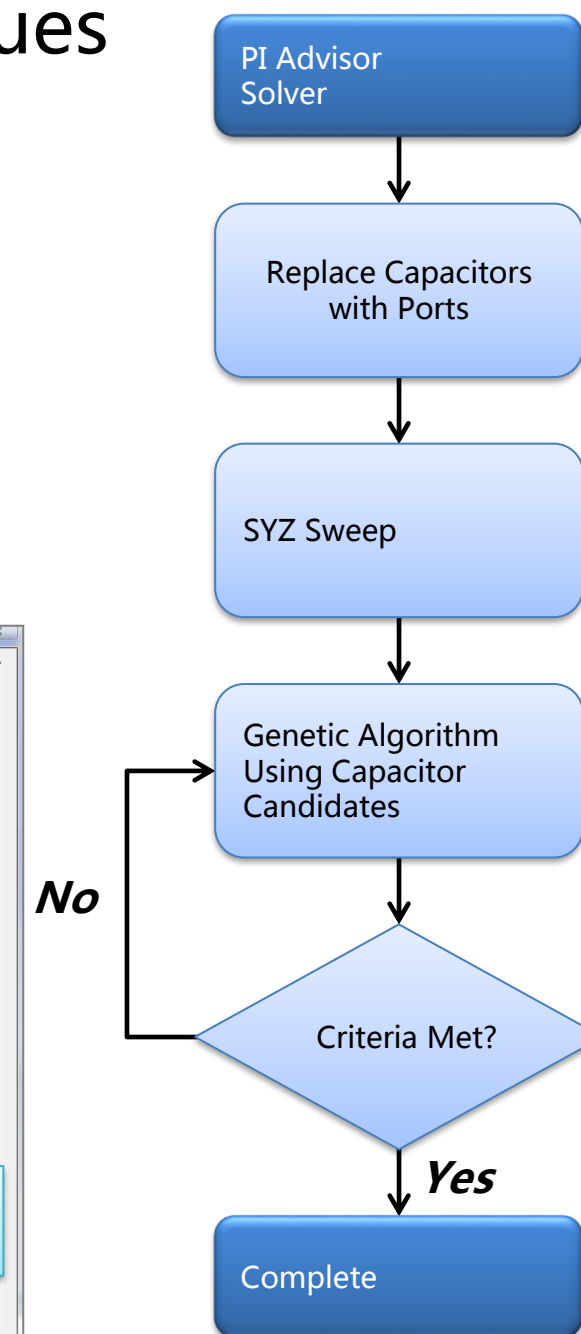
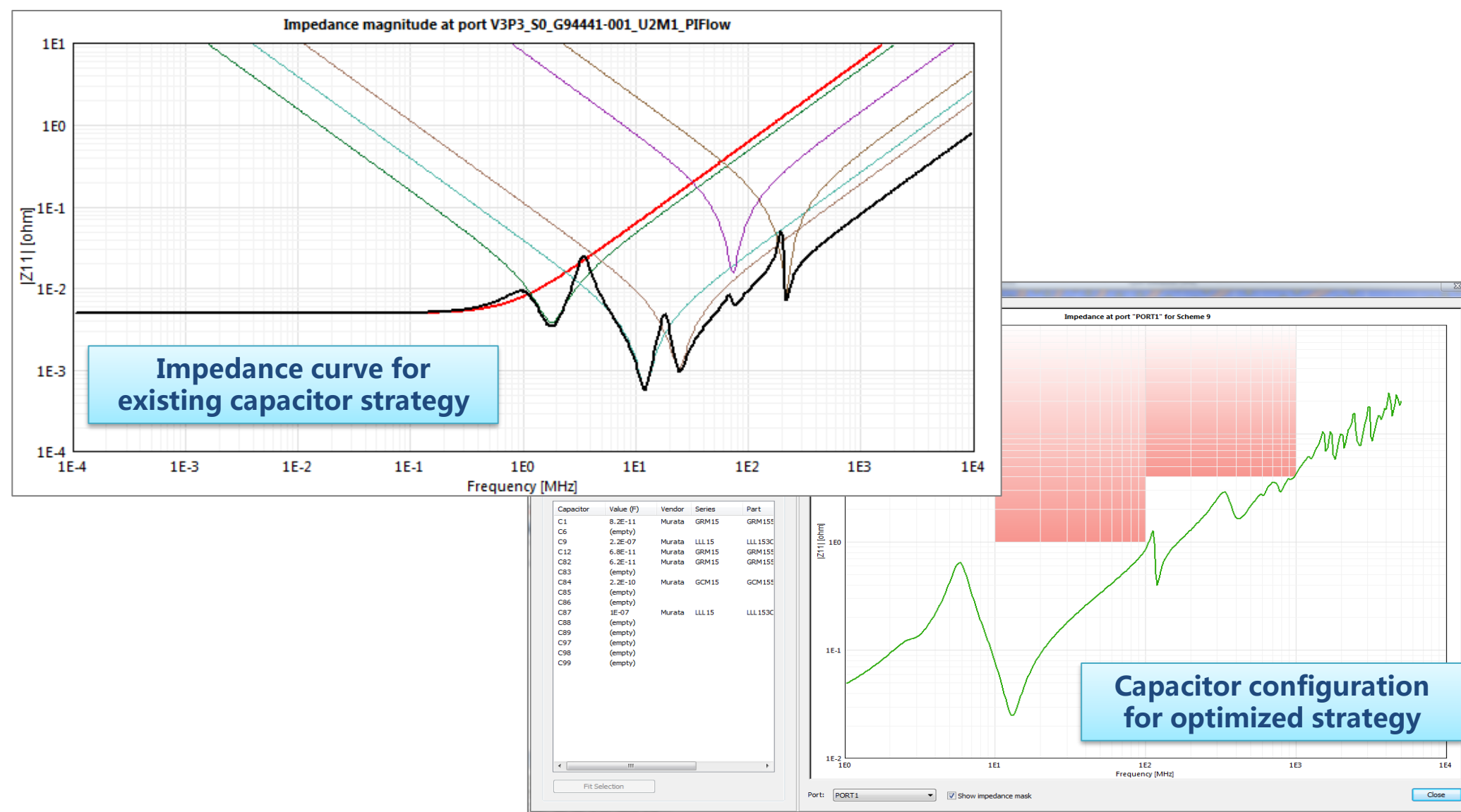
Full-wave extraction of entire PDN including:

- Board geometry
- Passive components



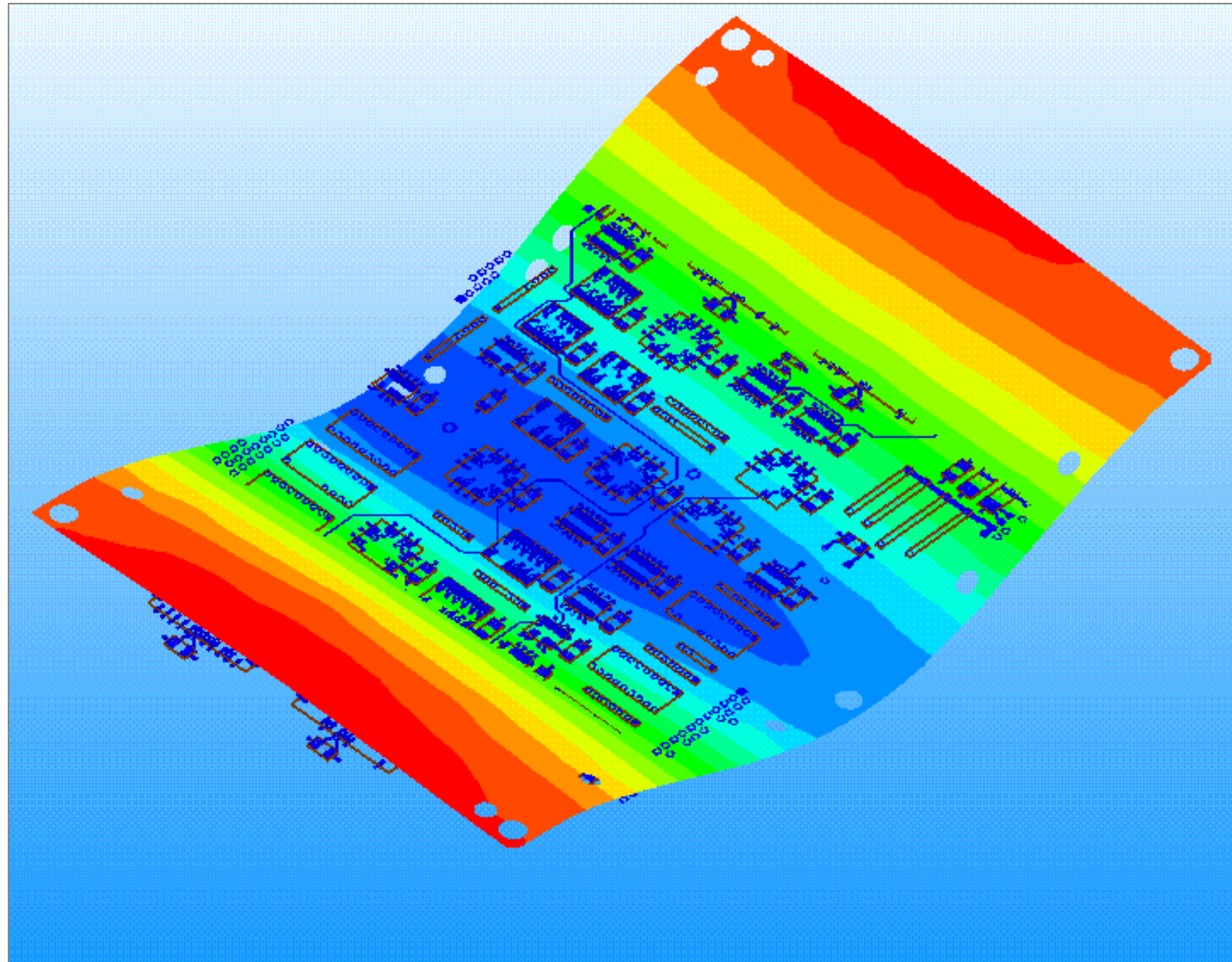
ANSYS SIwave—PI Advisor

- PI Advisor is an in-built tool that automatically optimizes De-coupling Capacitor Strategy for packages and boards
- Quick calculation for determining optimal capacitor values
- Optimization based on given impedance mask



ANSYS SIwave——Resonant Modes

- Resonant modes highlight potential problem areas of a PCB or Package
- Red and blue areas indicate high impedances at a particular frequency



目录

1. SIPI仿真必要性
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3. 新版本新功能

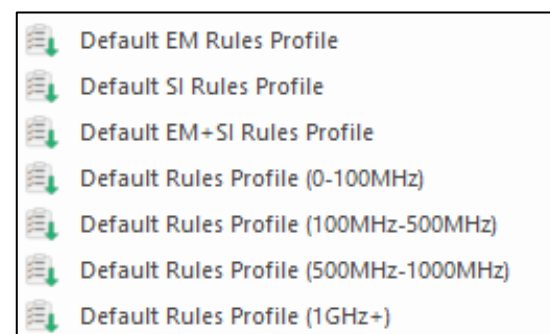
ANSYS SIwave新功能

- EMI Scanner –快速扫描整个设计，寻找可能导致EMI问题的违反规则的行为；
- Electromigration analysis电迁移分析 –利用电流和温度解析预测高风险MTTF区域；
- 改进了SIwave中的HFSS区域，允许分布式求解器和频率扫描，以及裁剪操作的清理；
- 层叠向导
- 背钻向导

EMI Scanner – “ERC” EMI Rules Checker

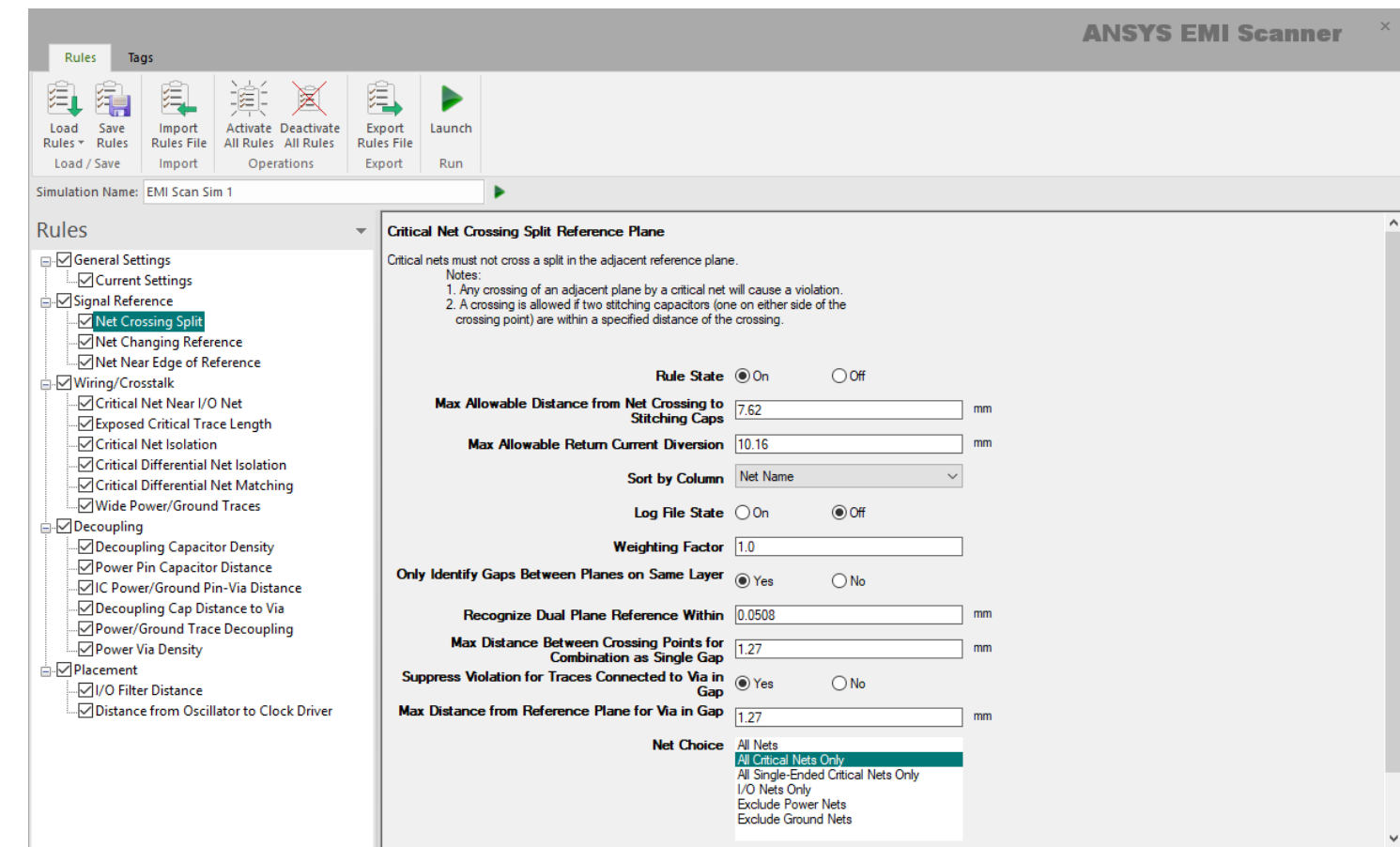
Included With SIwave license &
Available within SIwave or 3D Layout Design

- 对可能导致EMI/EMC问题的常见布局违规行为的全板分析
- 可用于不同操作条件和频率范围的示例规则集



- 规则文件可以导出/导入到简单的xml文件中

```
</param>
<param label="Recognize Dual Plane Reference Within" name="ALLOW DIST VARIATION" type="float">
  <description>Instructs EMI Scanner to consider both planes as a reference when checking</description>
  <value type="default">0.0508</value>
</param>
<param label="Net Choice" name="NET LISTING" type="single_select_list" view="advanced">
  <description>Specifies the type of Nets to include in this rule analysis.</description>
  <value altvalue="ALL">All Nets</value>
  <value altvalue="CRITICAL" type="default">All Critical Nets Only</value>
  <value altvalue="SINGLE_CRITICAL">All Single-Ended Critical Nets Only</value>
  <value altvalue="IO">I/O Nets Only</value>
</param>
</rule>
</ruletype>
```

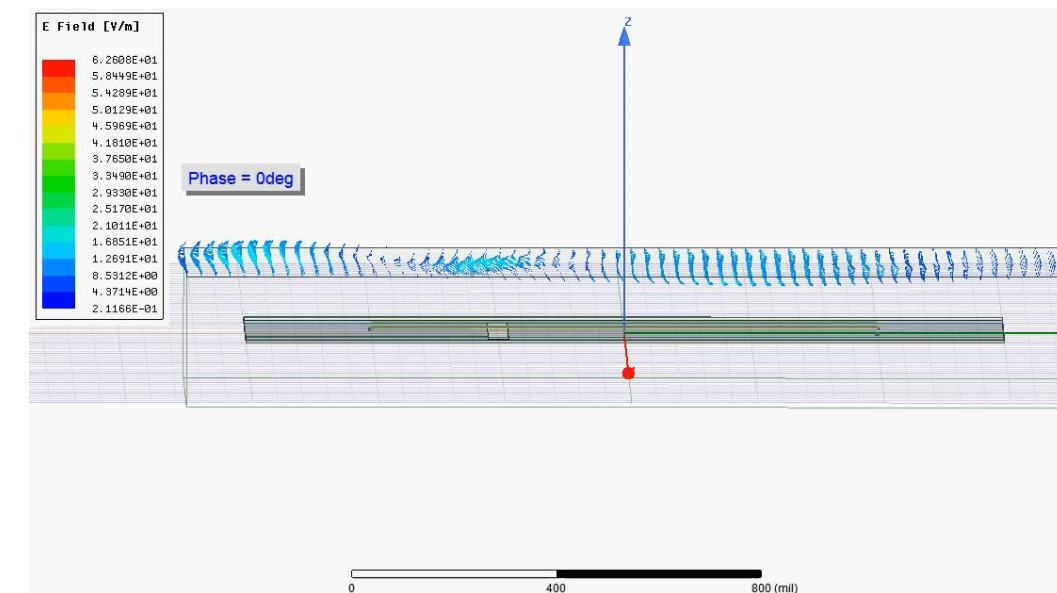


通过在设计过程的早期提供洞察力，显著地减少了对EMI遵从性的验证

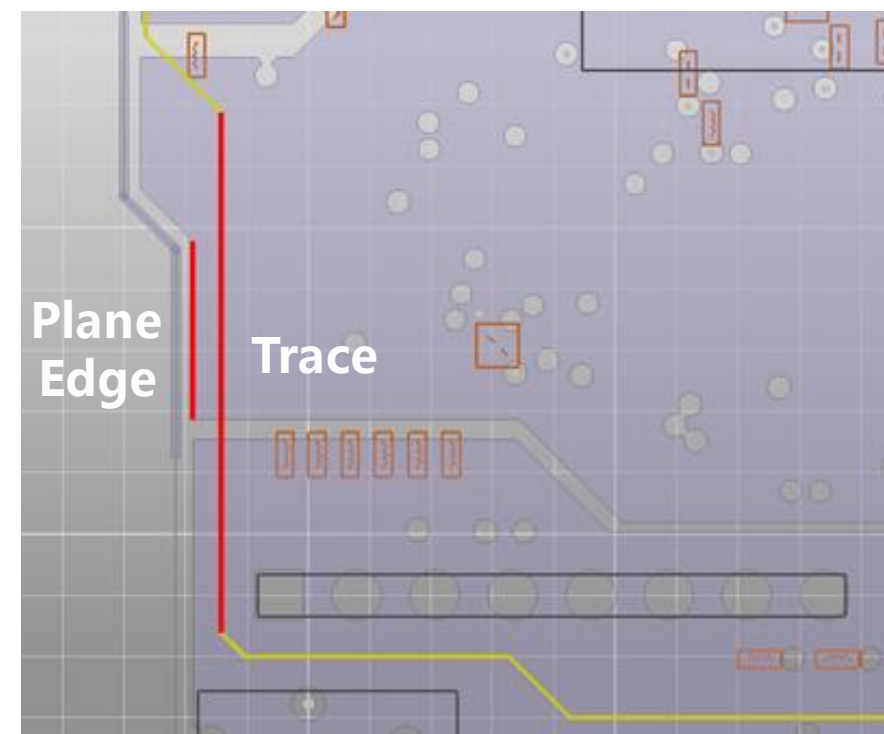
电磁干扰规则

- Signal Reference
 - Net Crossing Split
 - Net Changing Reference
 - Net Near Edge of Reference
- Wiring/ Crosstalk
 - Critical Net Near I/O Net
 - Exposed Critical Trace Length
 - Critical Net Isolation
 - Critical Differential Net Matching
- Placement
 - I/O Filter Distance
 - Distance from Oscillator to Clock Driver

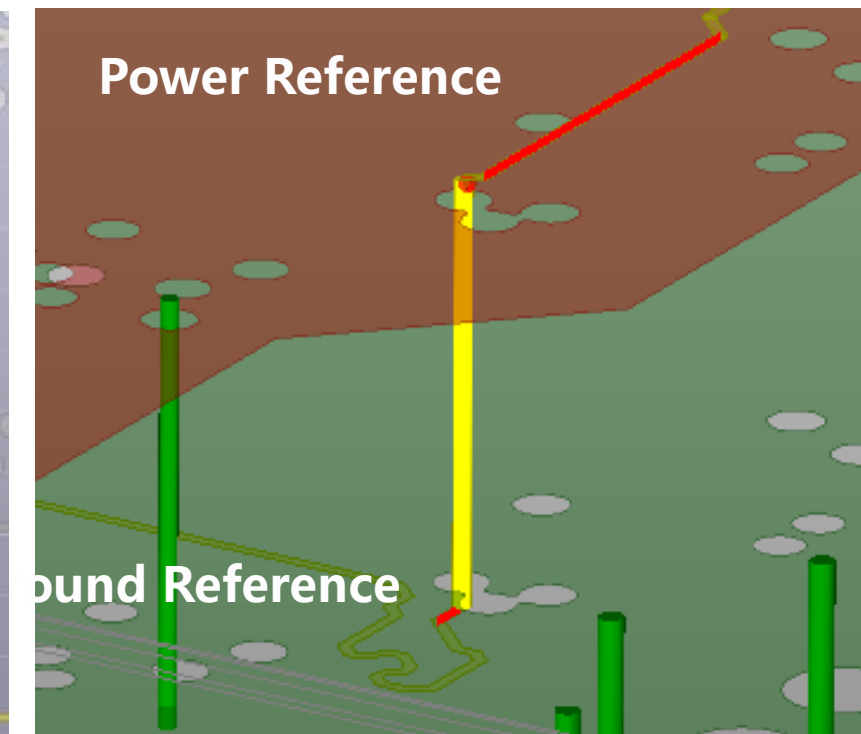
Net Crossing Split



Net Near Edge of Reference



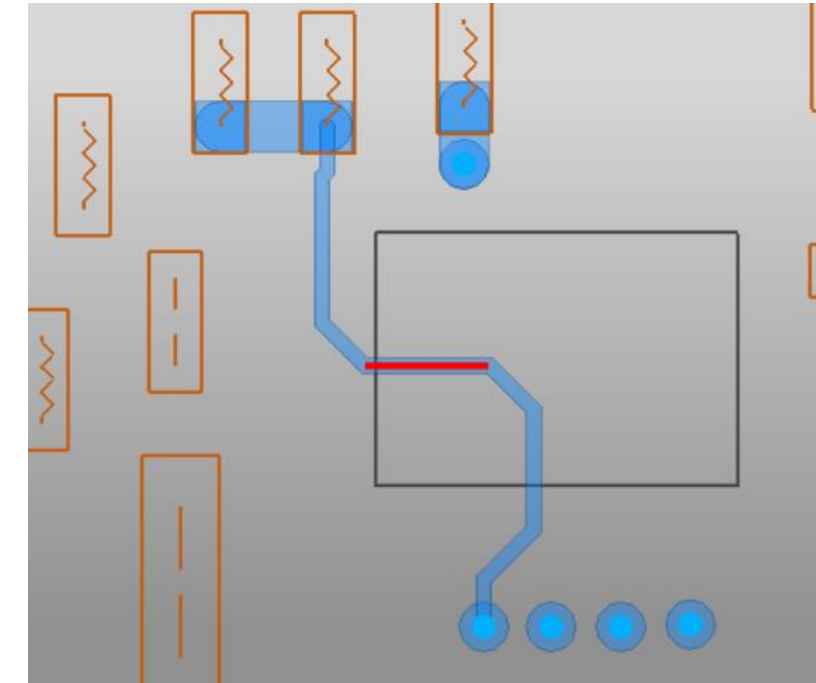
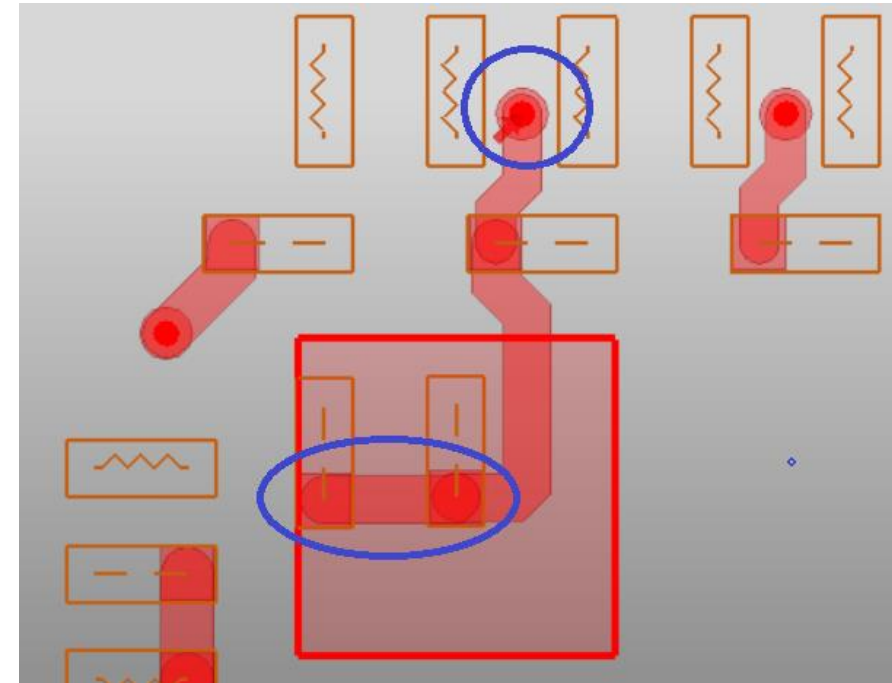
Net Changing Reference



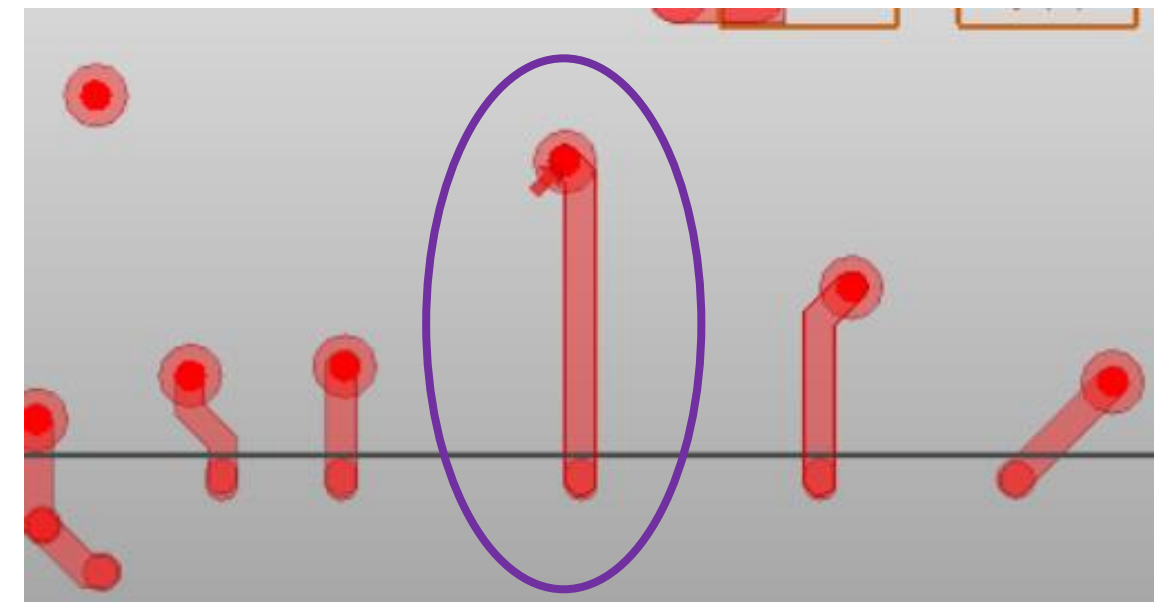
电源完整性规则

- Wiring
 - Wide Power/Ground Traces
- Decoupling
 - Decoupling Capacitor Density
 - Power Pin to Capacitor Distance
 - IC Power/Ground Pin to Via Distance
 - Decoupling Cap Distance to Via
 - Power/Ground Trace Decoupling
 - Power Via Density

Decoupling Capacitor Distance to Via Wide Power/Ground Trace Check



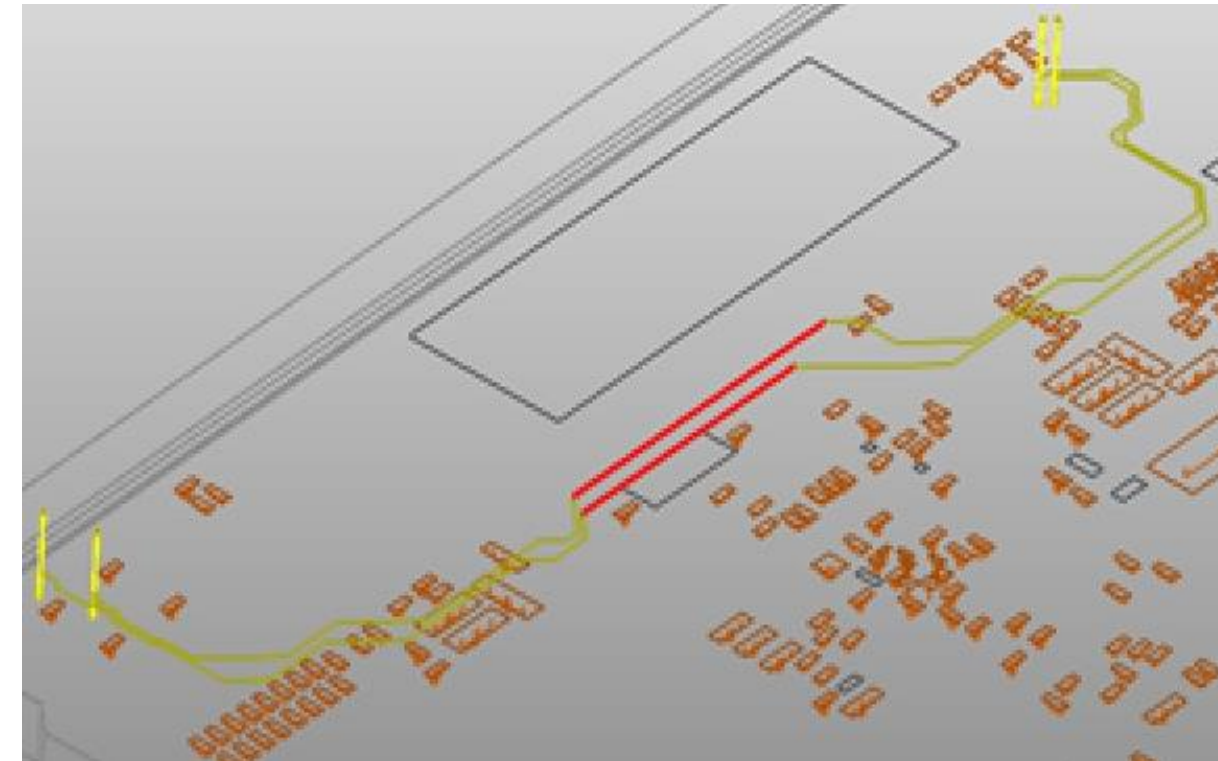
IC Power Pin to Via Distance



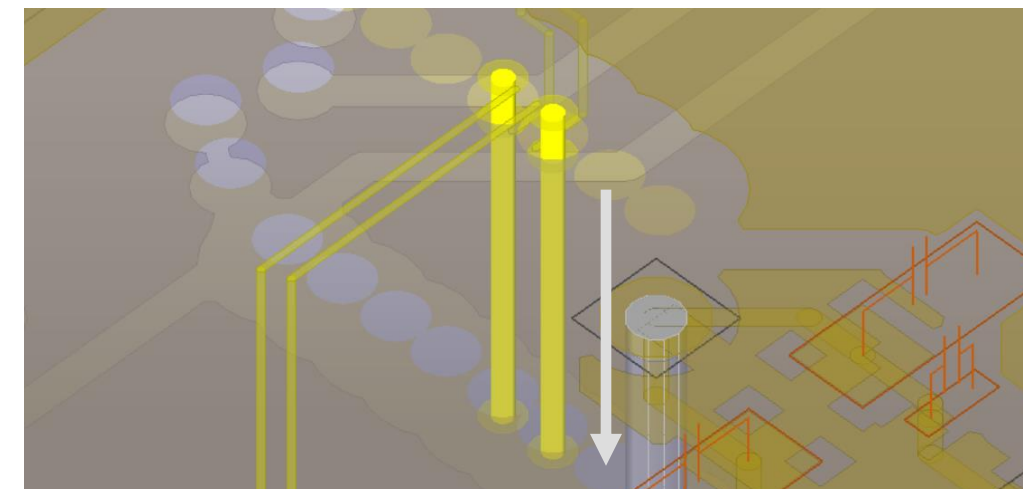
网络和过孔完整性规则

- Net Integrity
 - Net to Net Coupling
 - Net Stubs
 - Net Crossing Split
 - Critical Net routing between Reference Planes
 - Diff Pair Running Skew
- Via Integrity
 - Via to Net Coupling
 - Via Stub Length

Net to Net Coupling



Via Stub Length



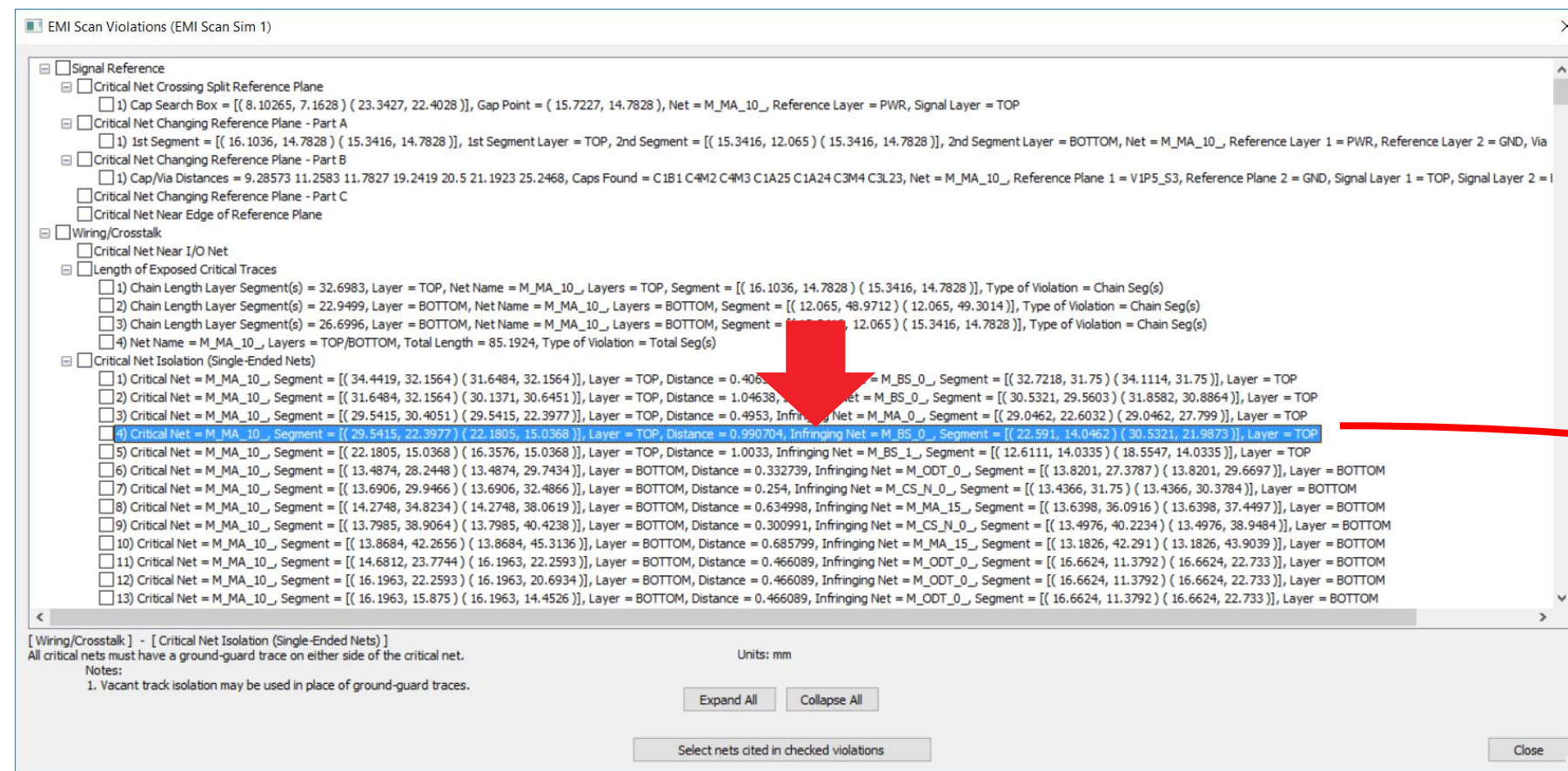
EMI扫描输出

Included With SIwave license &
Available within SIwave or 3D Layout Design

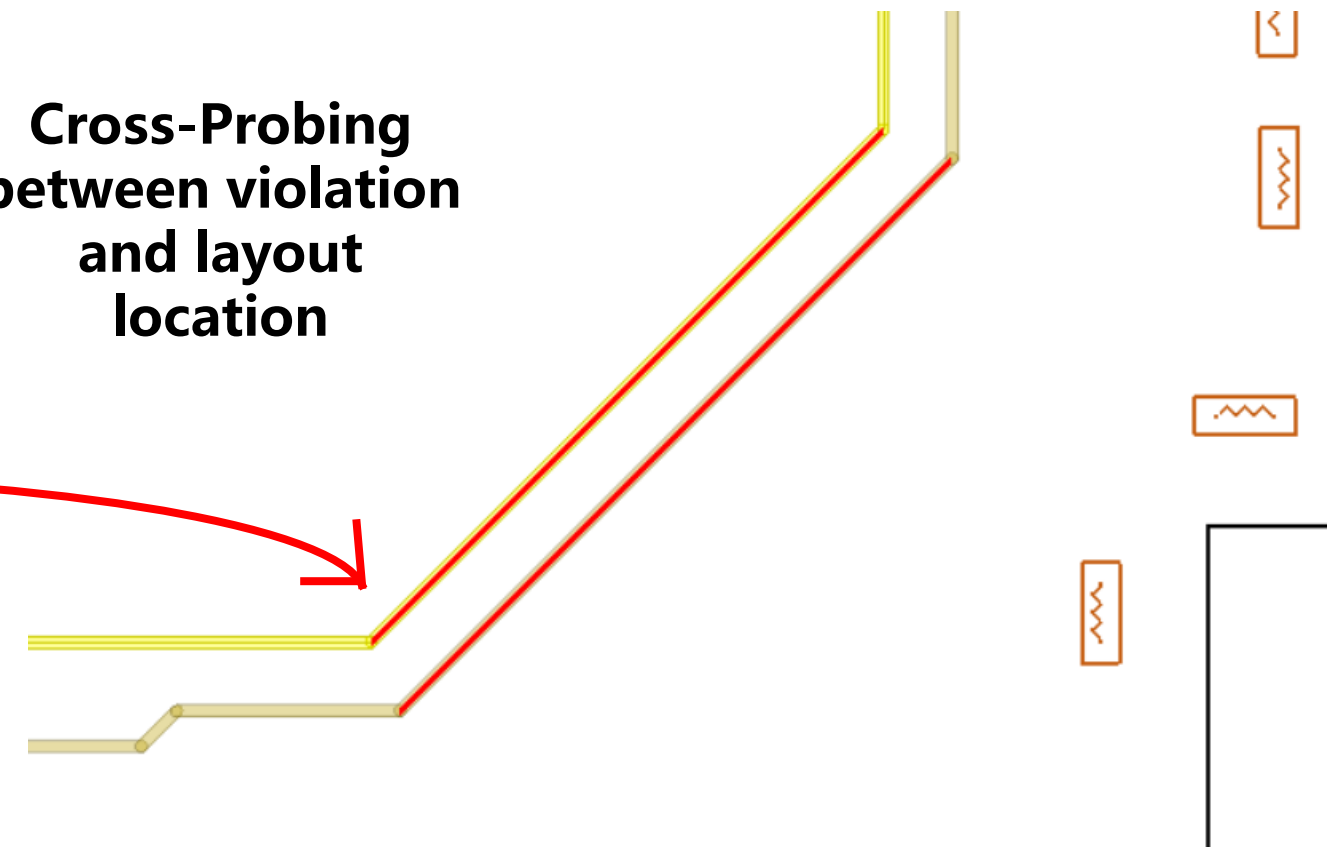
- 违规行为按类型显示
- 在列表中选择冲突高亮显示布局中的违规位置

Violation List

Layout View



Cross-Probing
between violation
and layout
location



电迁移分析

- 使用Black方程预测平均失效时间(MTTF), 突出潜在关注区域
- 需要直流压降仿真
- 也可以通过包含Icepak结果来包括温度效应

Compute Electromigration Induced Failures

Simulation name: EMF Sim 1

Black's Equation: $MTTF = A_j^{-n} e^{\left(\frac{E_a}{kT}\right)}$

Black's Equation Parameters

Material Name	Experimental Constant (A)	Activation Energy (Ea)
copper	1	1eV

Warn if MTTF less than: 90000hour

Error if MTTF less than: 45000hour

Piecewise constant values for n

Current Density Start	Current Density End	Value of n
0A_per_cm2	1000A_per_cm2	1
1000A_per_cm2	10000A_per_cm2	1.5
10000A_per_cm2	1e+99A_per_cm2	2

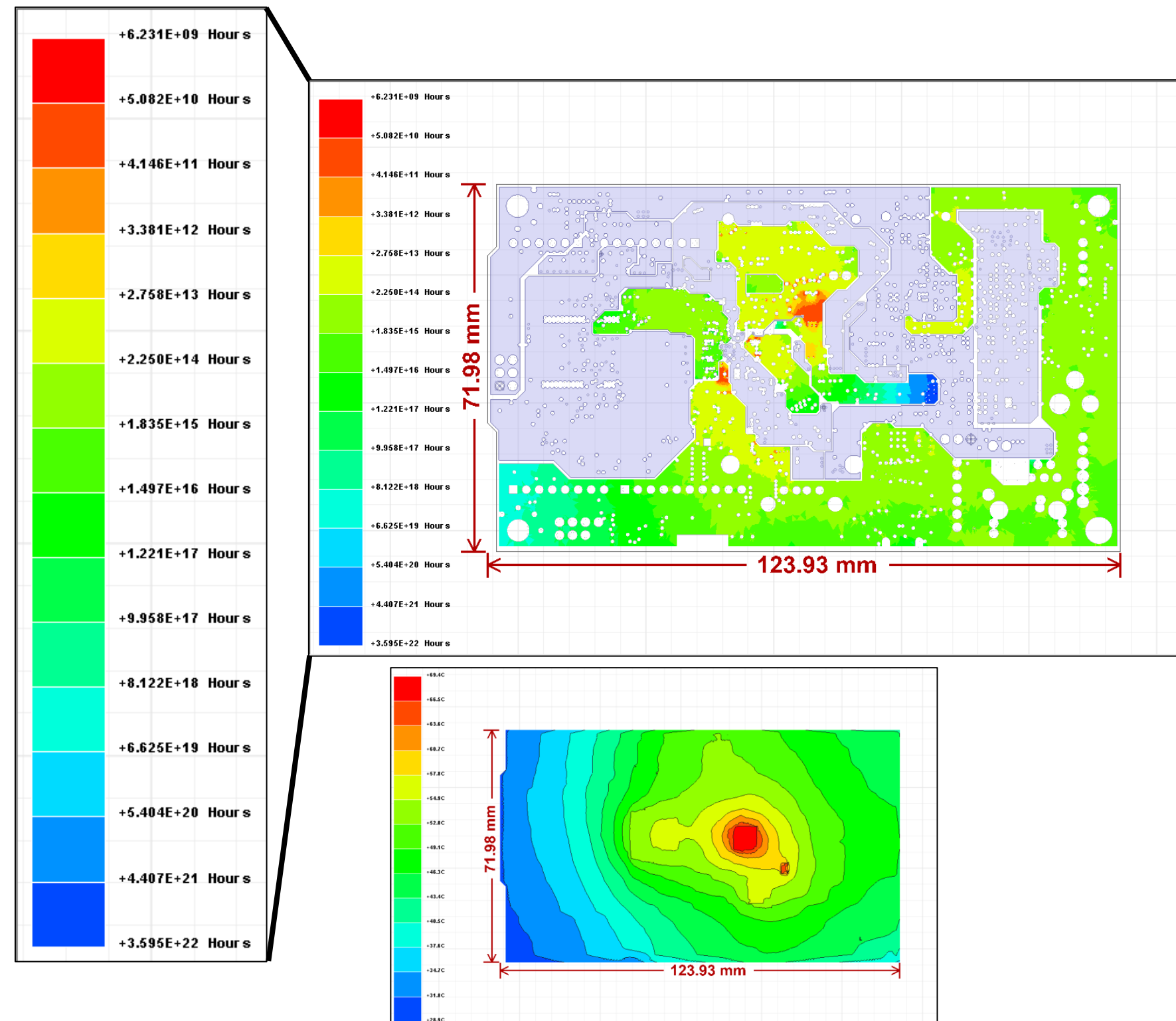
Use current density from DC IR simulation: DC IR Sim 1

☒ Apply uniform temperature of: 25cel

☐ Use temperature distribution from Icepak simulation:

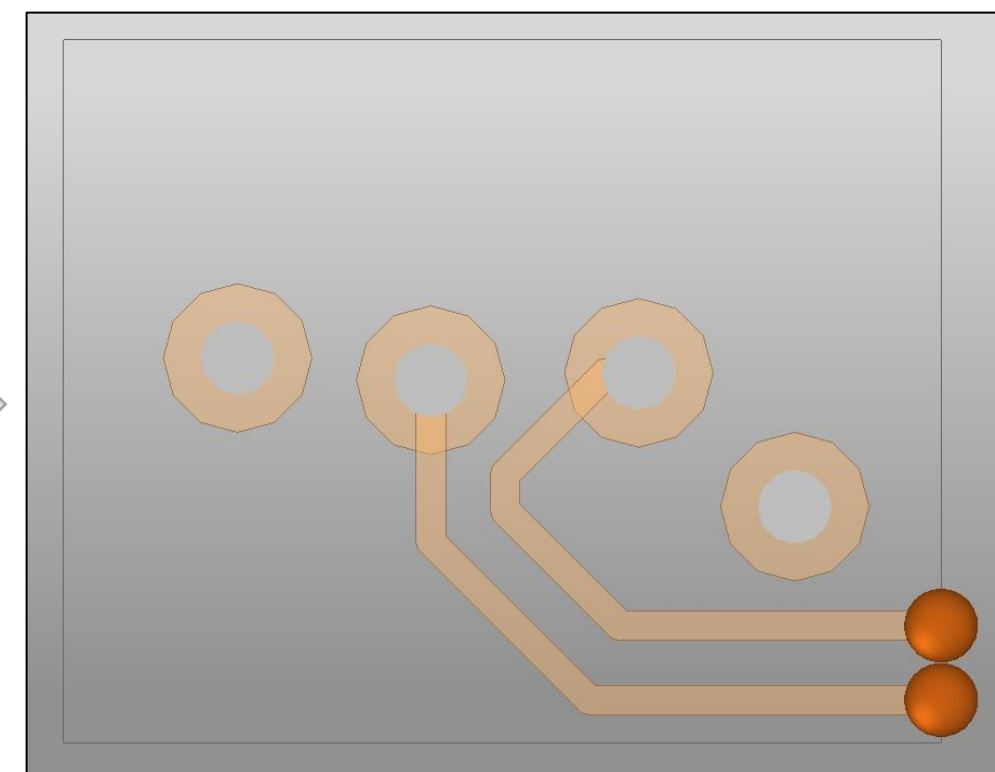
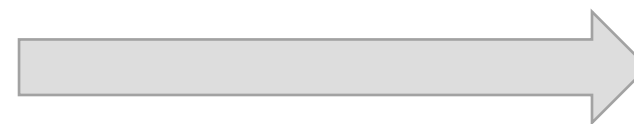
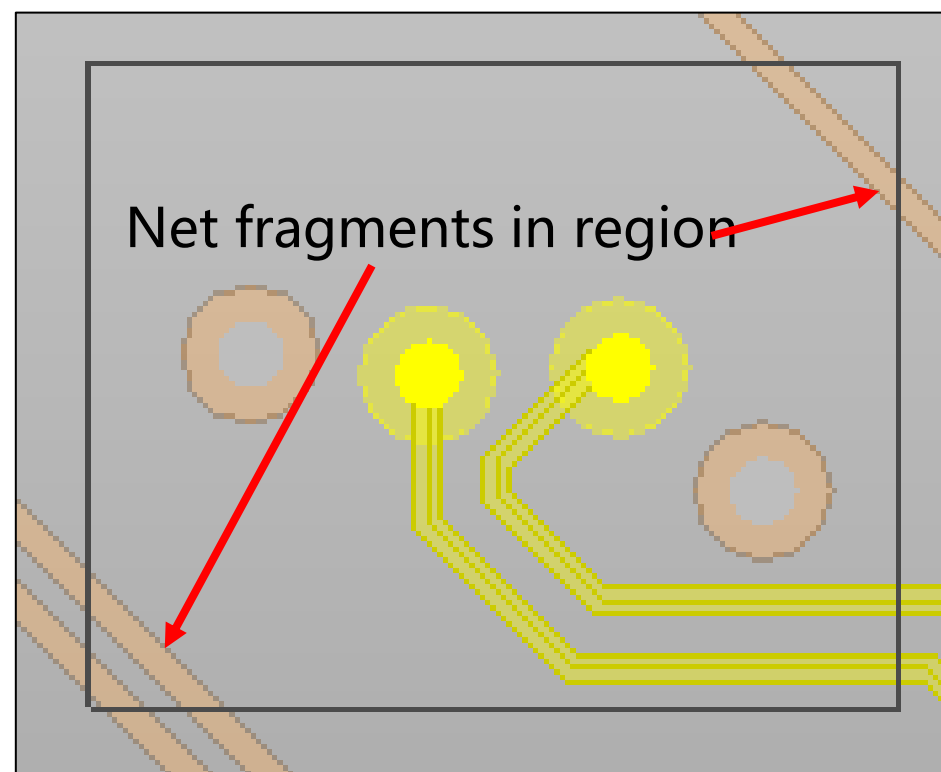
Save Settings Launch Cancel

Included With SIwave license



HFSS Regions in SIwave

- Released in R19.1
- 2019 R1增强
 - 每个区域的并行化频率扫描
 - 区域串联求解
 - 与独立分布式程序或调度程序兼容
 - 清理个别区域



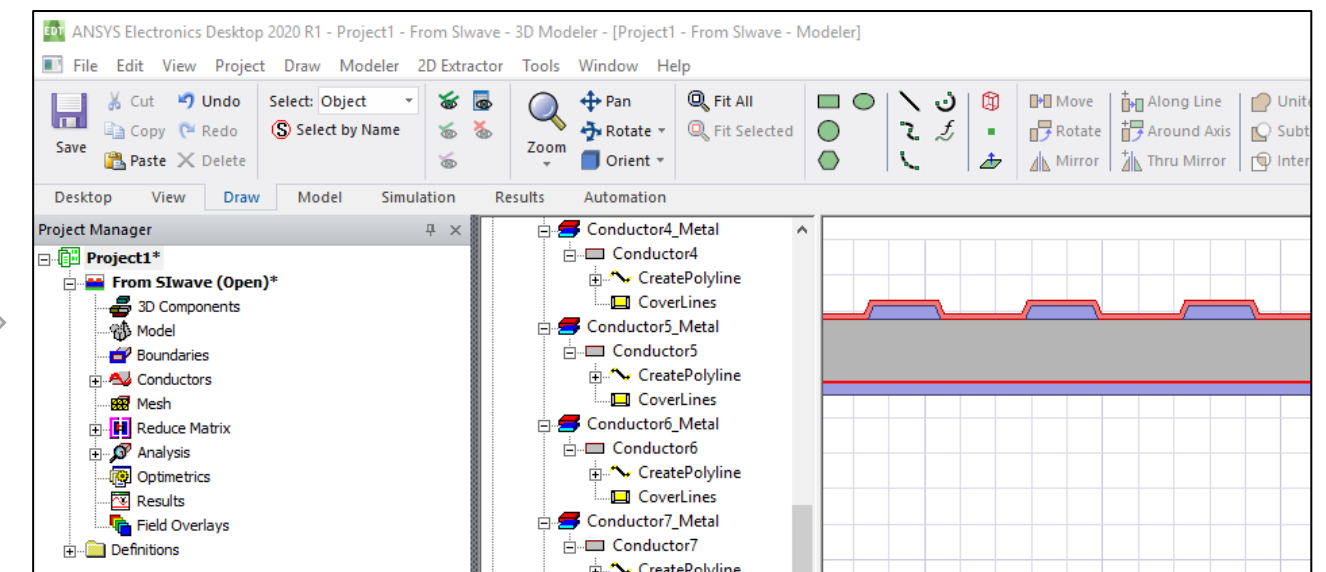
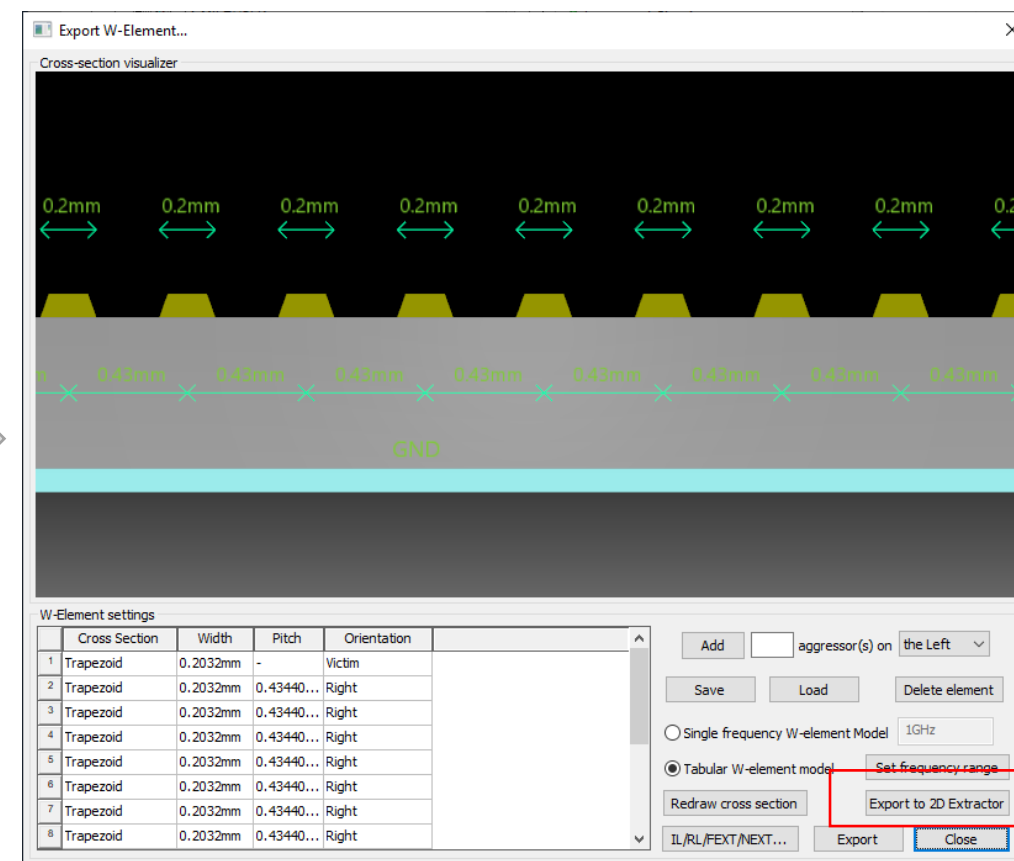
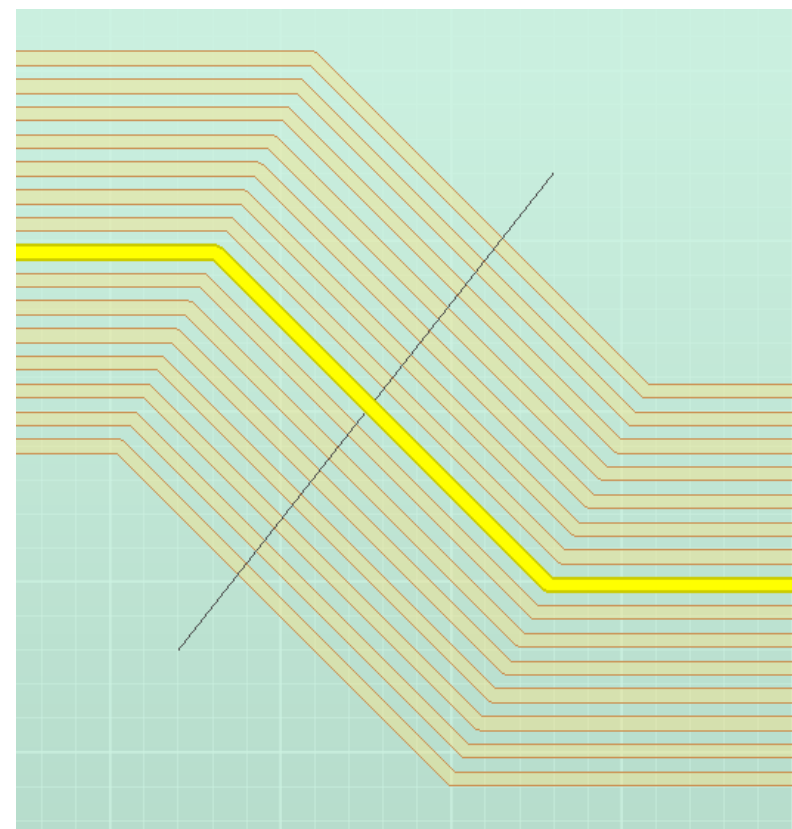
Net fragments eliminated for HFSS

- Reduced mesh / solve time for region

Stackup Wizard Enhancements - W-element Analysis

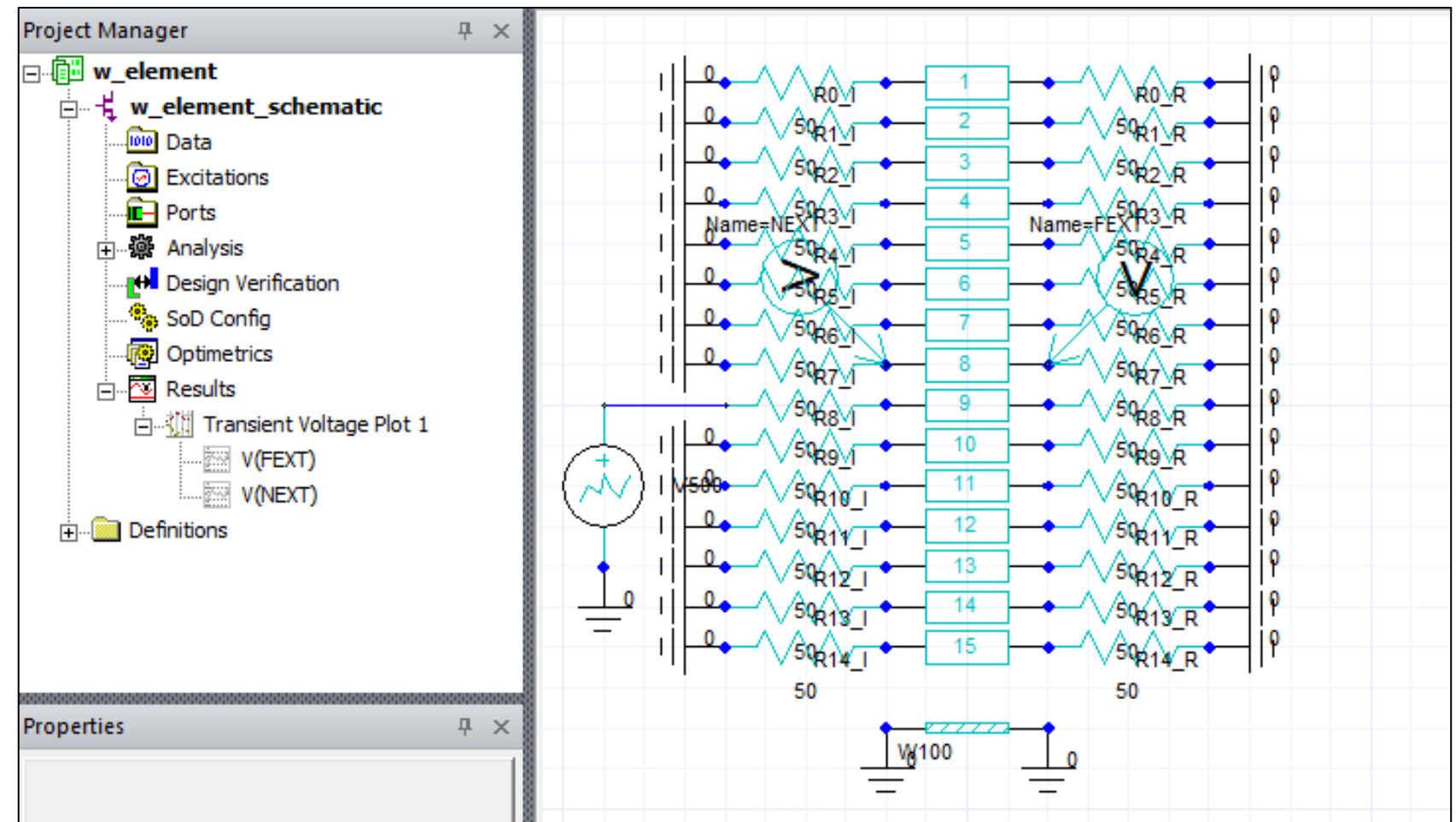
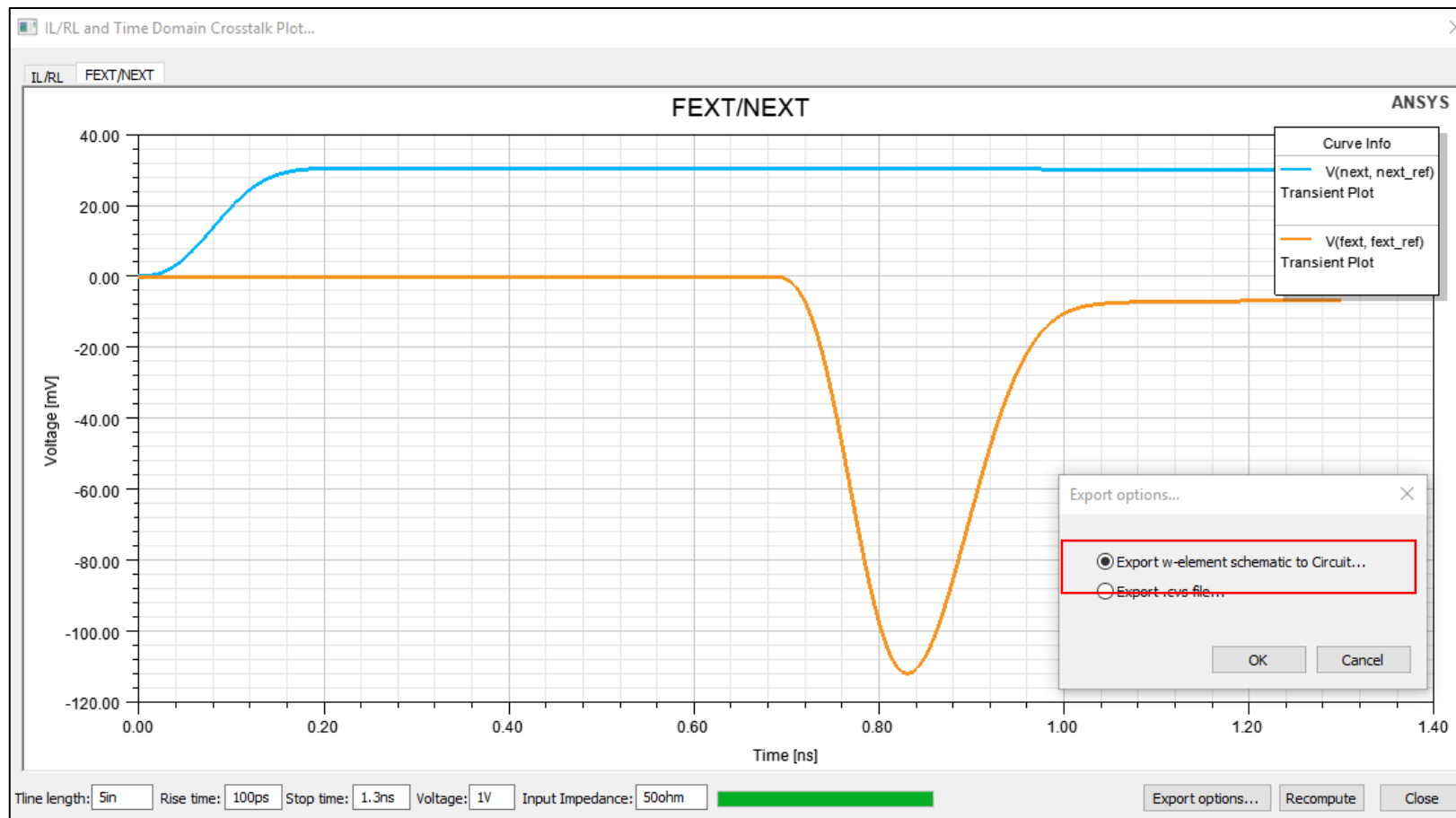
- Draw polyline which crosses traces in layout to populate W-element export dialog
- Export W-element as well as 2D Extractor project

Select "victim" trace



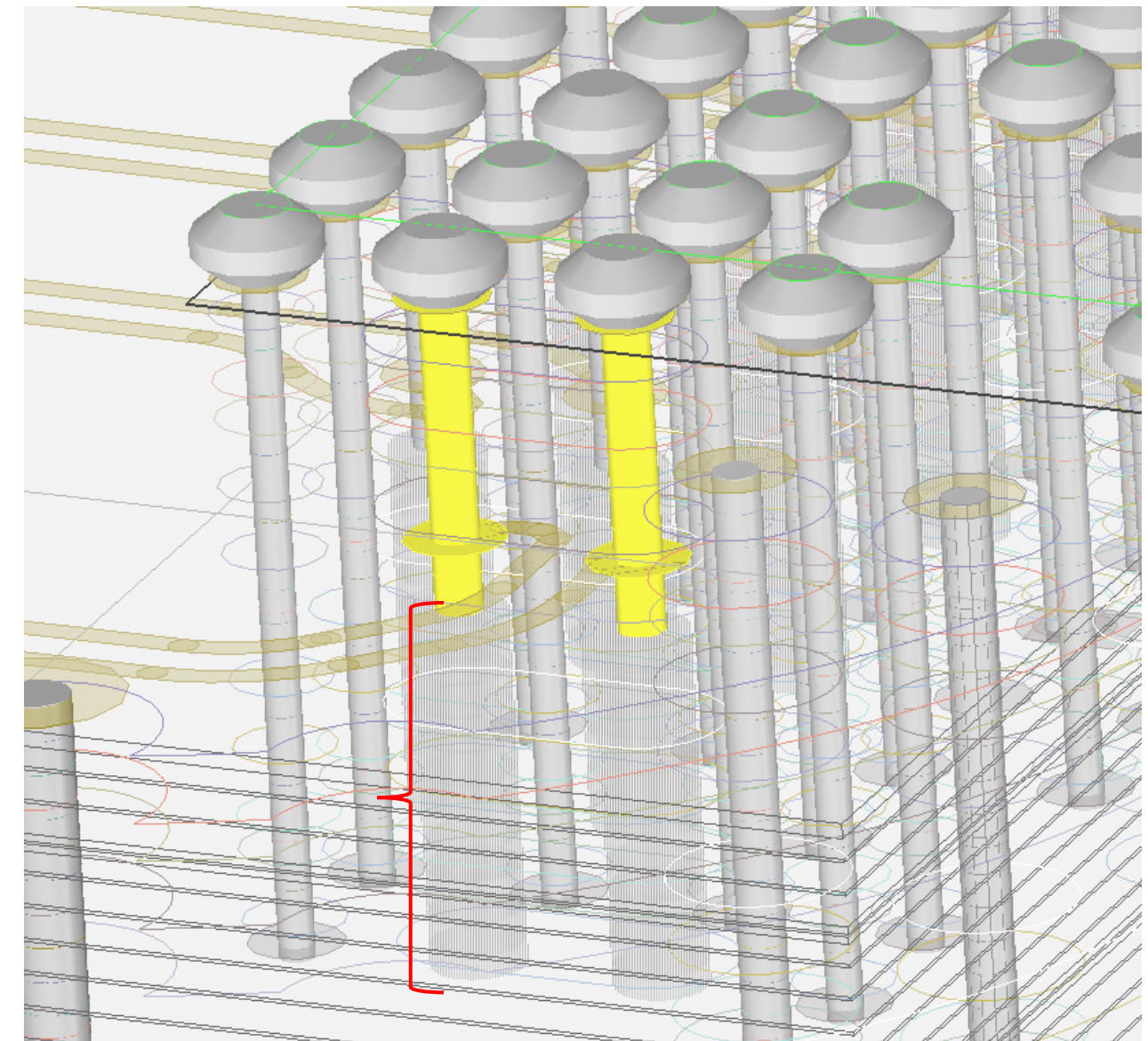
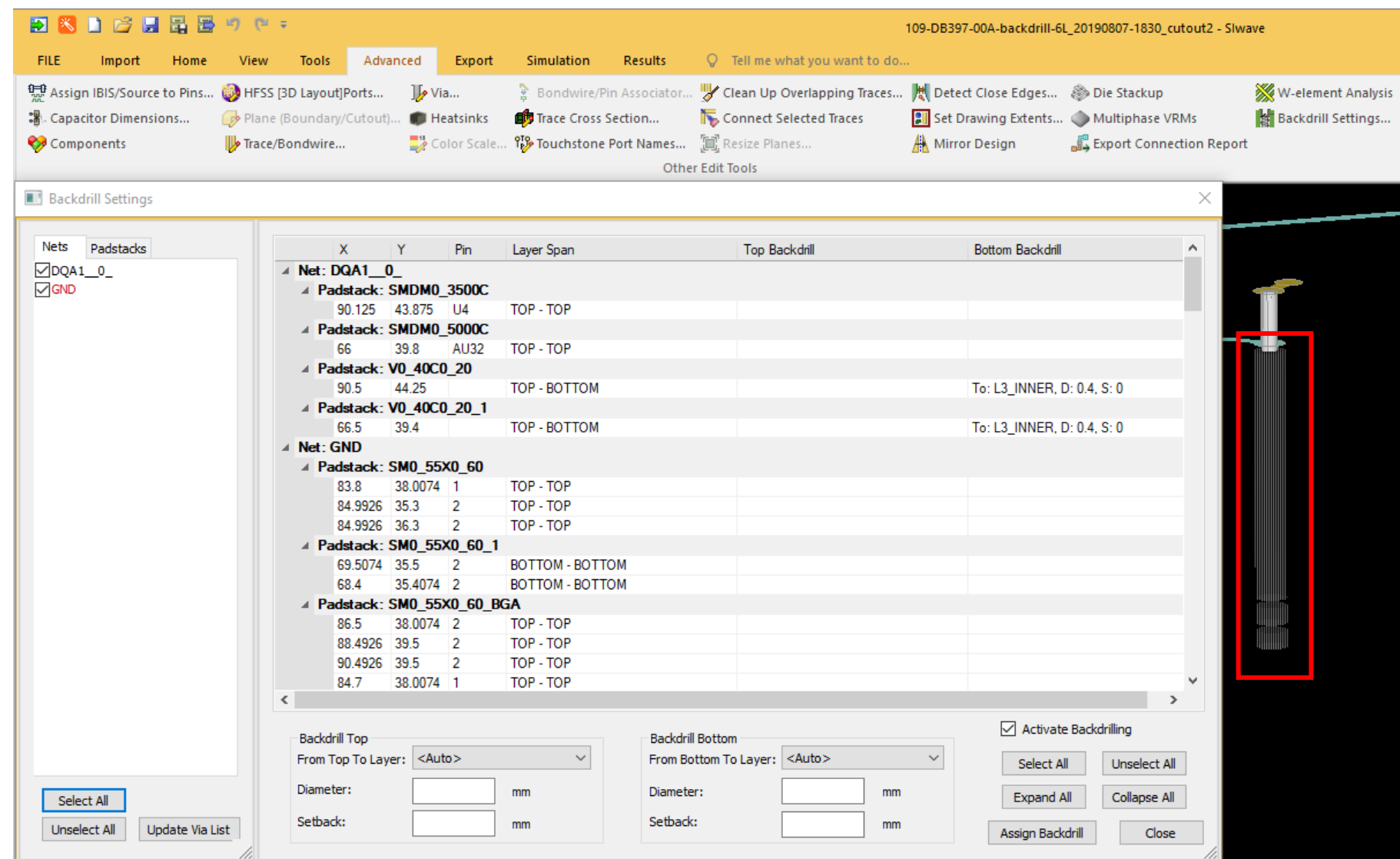
Stackup Wizard Enhancements

- Export preconfigured schematics to AEDT for detailed IL/RL and FEXT/NEXT sims



Via Backdrill Configuration UI

- Backdrill information imported from ODB++ and 3D Layout
- Support for setback distances

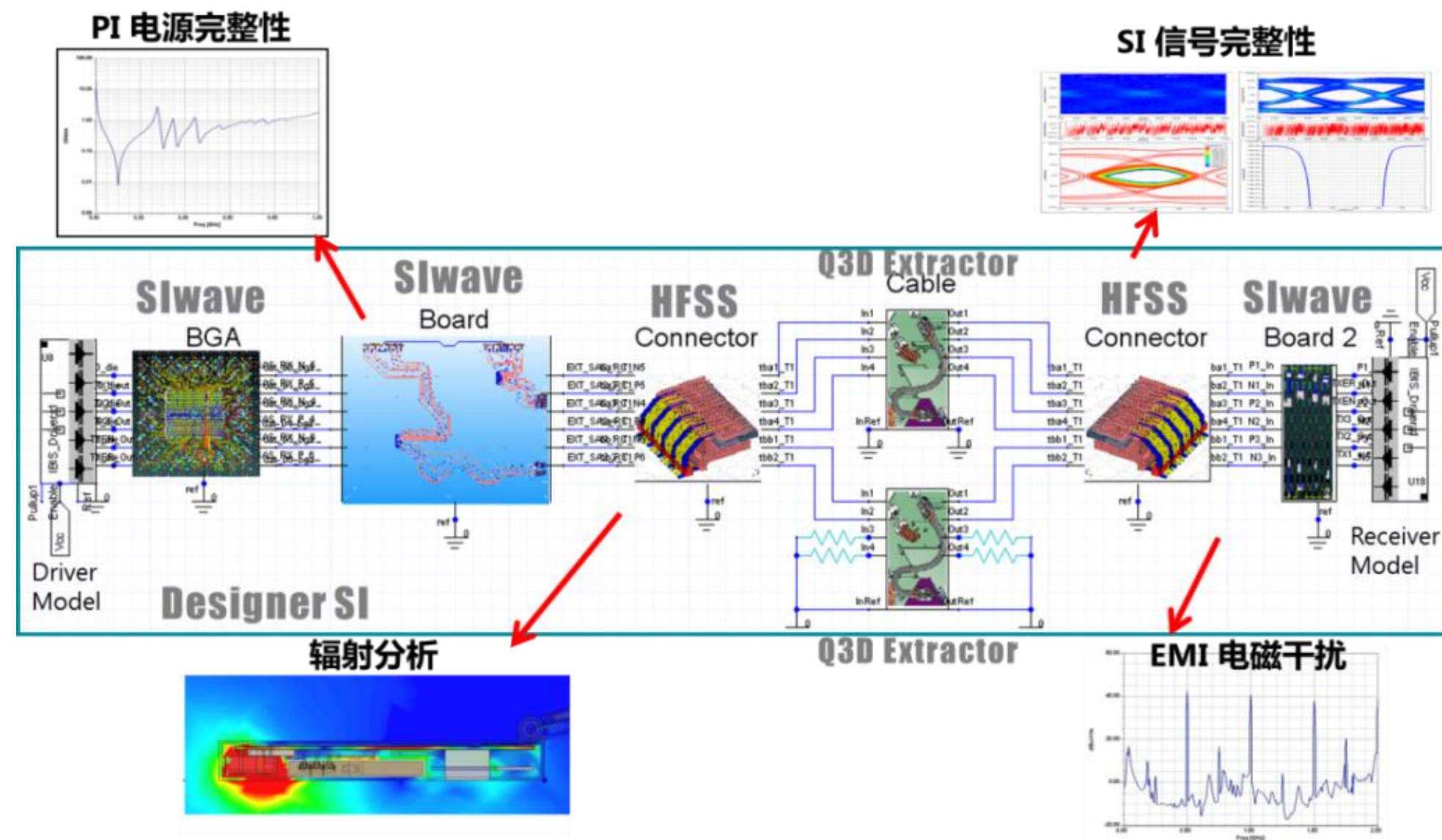


Vias stub drilled out

小结

随着通信技术的发展，及对信号传输速率的要求飞速提升，电子产品设计要求越来越苛刻，创新产品设计越来越依赖于高频电磁场仿真。

在这一领域，ANSYS凭借强大的电磁场仿真平台，多个仿真器的综合应用，加速了电子产品的研发进程。



感谢倾听

期待与您的进一步合作 😊



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